



# IEEE SW Test Workshop

## Semiconductor Wafer Test Workshop

June 9 - 12, 2013 | San Diego, California

# The Cost of Quality – Challenges of High-Volume Memory Wafer Test



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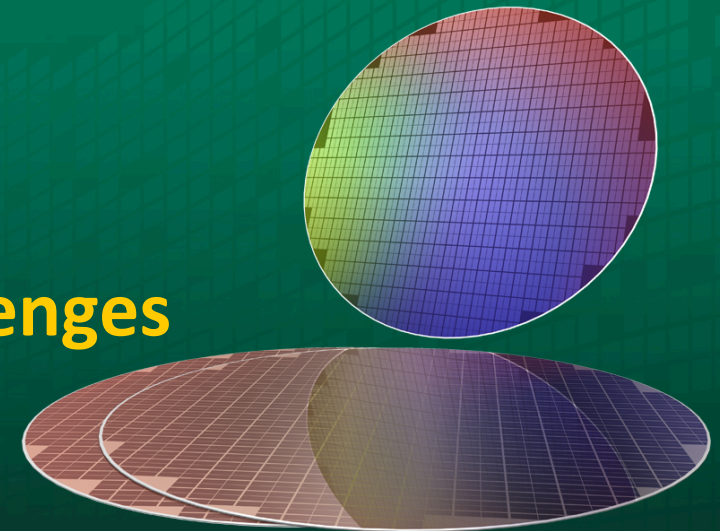
John Caldwell

Aaron Woodard

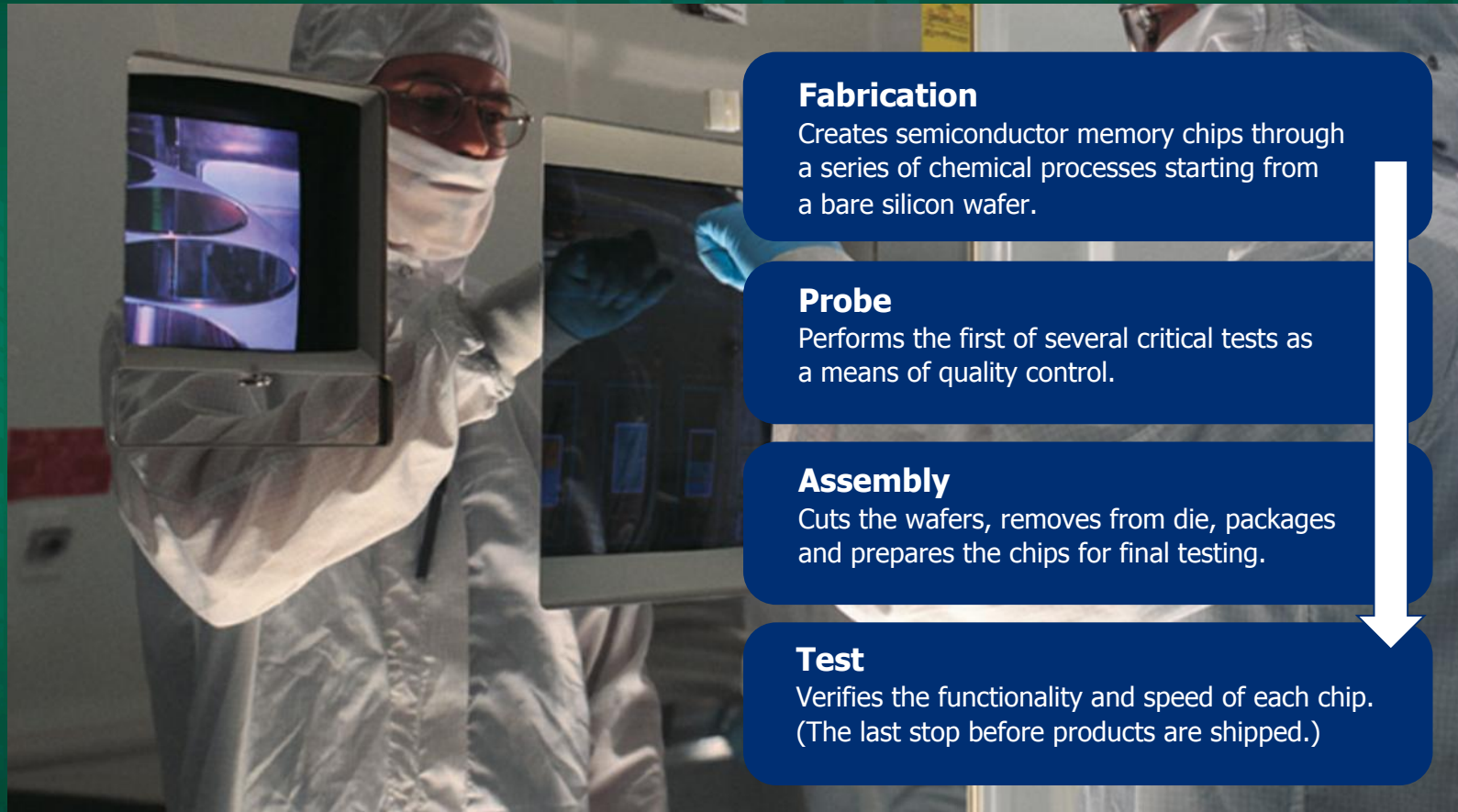
Jarod Hunter

# Agenda

- **Basics: Making of a Micron Memory Chip**
- **Product Portfolio and Industry Landscape**
- **Cost of Quality (Cost of Poor Quality)**
- **High-Frequency Wafer Test**
- **Bond Pad Damage**
- **Test Cell Stacking Tolerances**
- **Thermal Management**
- **Future Memory Product Challenges**
- **Conclusions**



# Basics: The Making of a Micron Memory Chip



## **Fabrication**

Creates semiconductor memory chips through a series of chemical processes starting from a bare silicon wafer.

## **Probe**

Performs the first of several critical tests as a means of quality control.

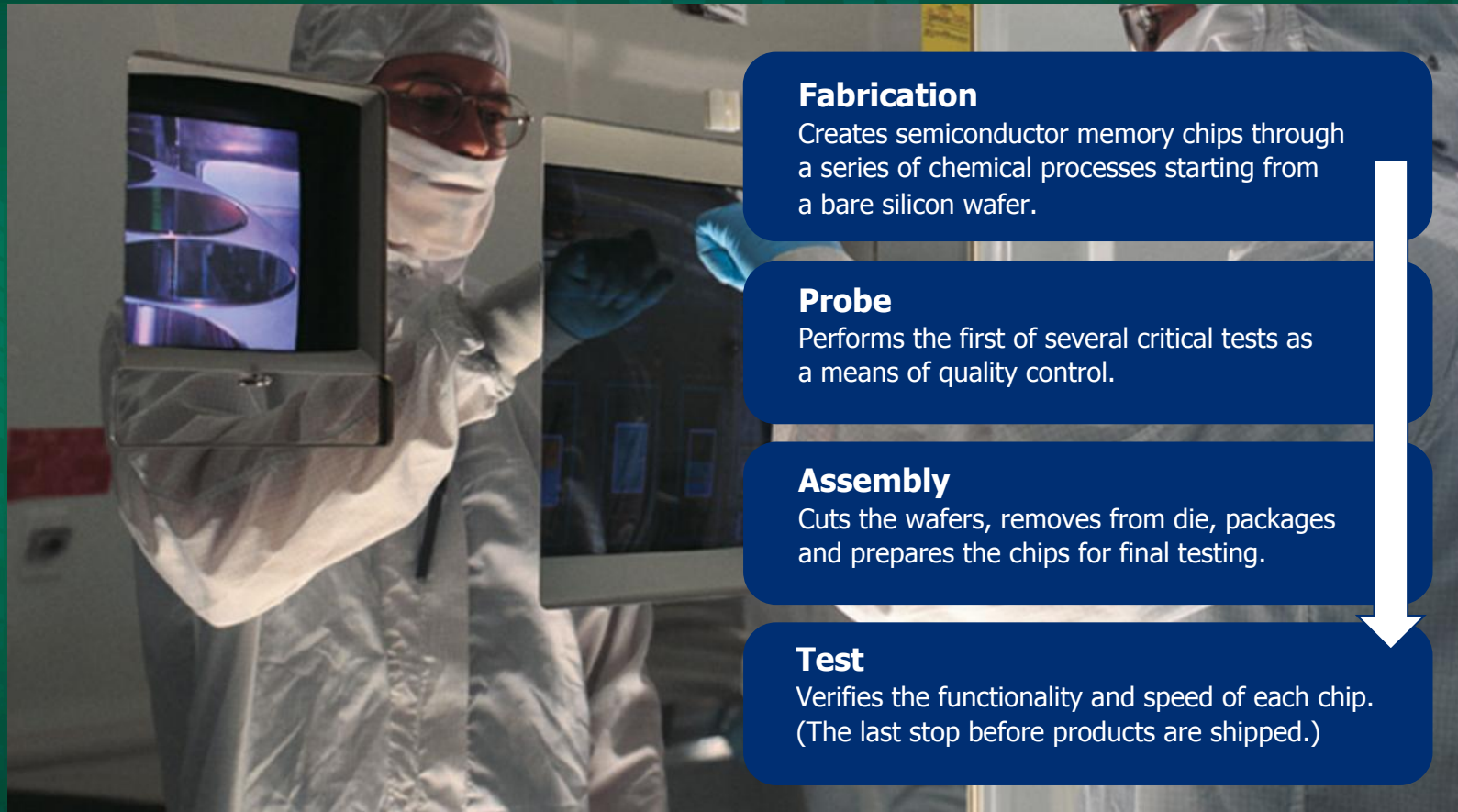
## **Assembly**

Cuts the wafers, removes from die, packages and prepares the chips for final testing.

## **Test**

Verifies the functionality and speed of each chip. (The last stop before products are shipped.)

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**In reality its not that simple**

# Diversifying Memory Markets

**Automotive**



**Storage**



**Graphics/Consumer**



**Networks**



**Server**



**Mobile**



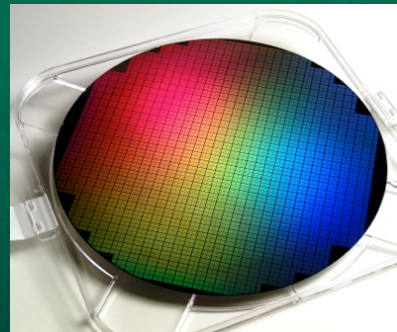
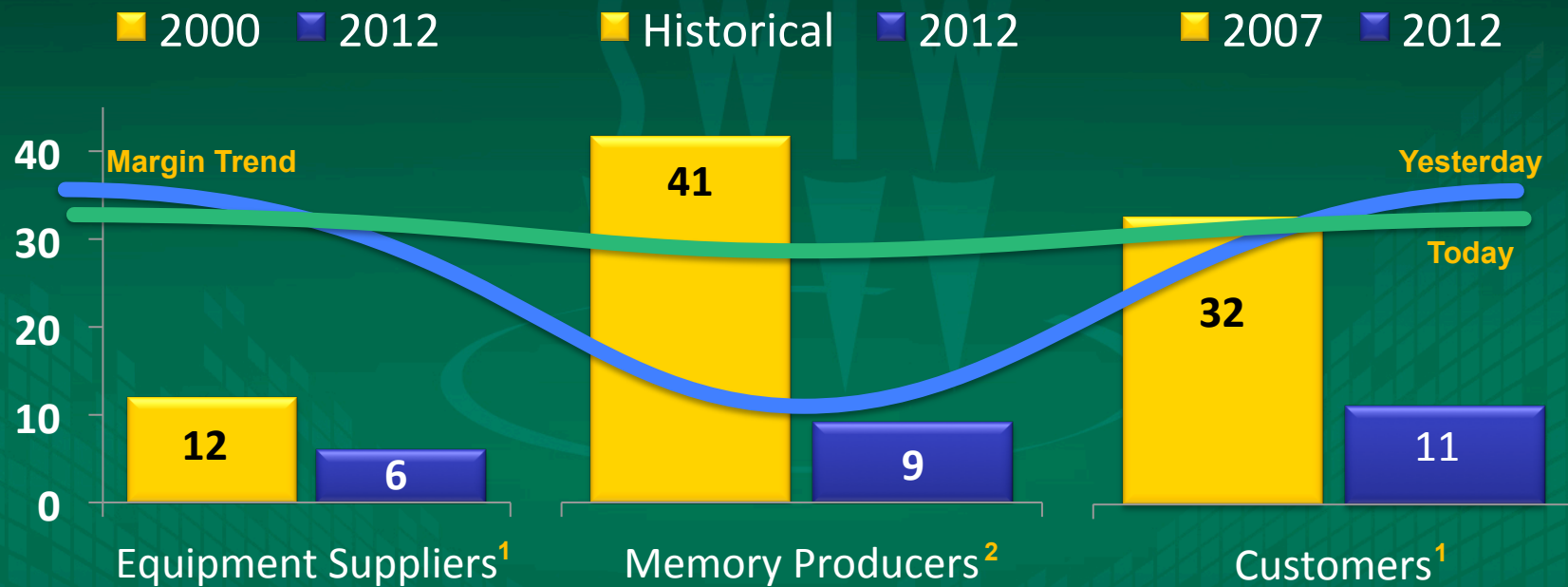
**Personal Computing**



**IMM**



# A New Industry Landscape



Source: Gartner, Micron Market Research Estimates

<sup>1</sup> Number of companies making up 60% or more of revenue

<sup>2</sup> Total memory producers

# Traditional View of Quality Costs

- Initial quality costs typically include only the most visible factors, i.e. above the iceberg

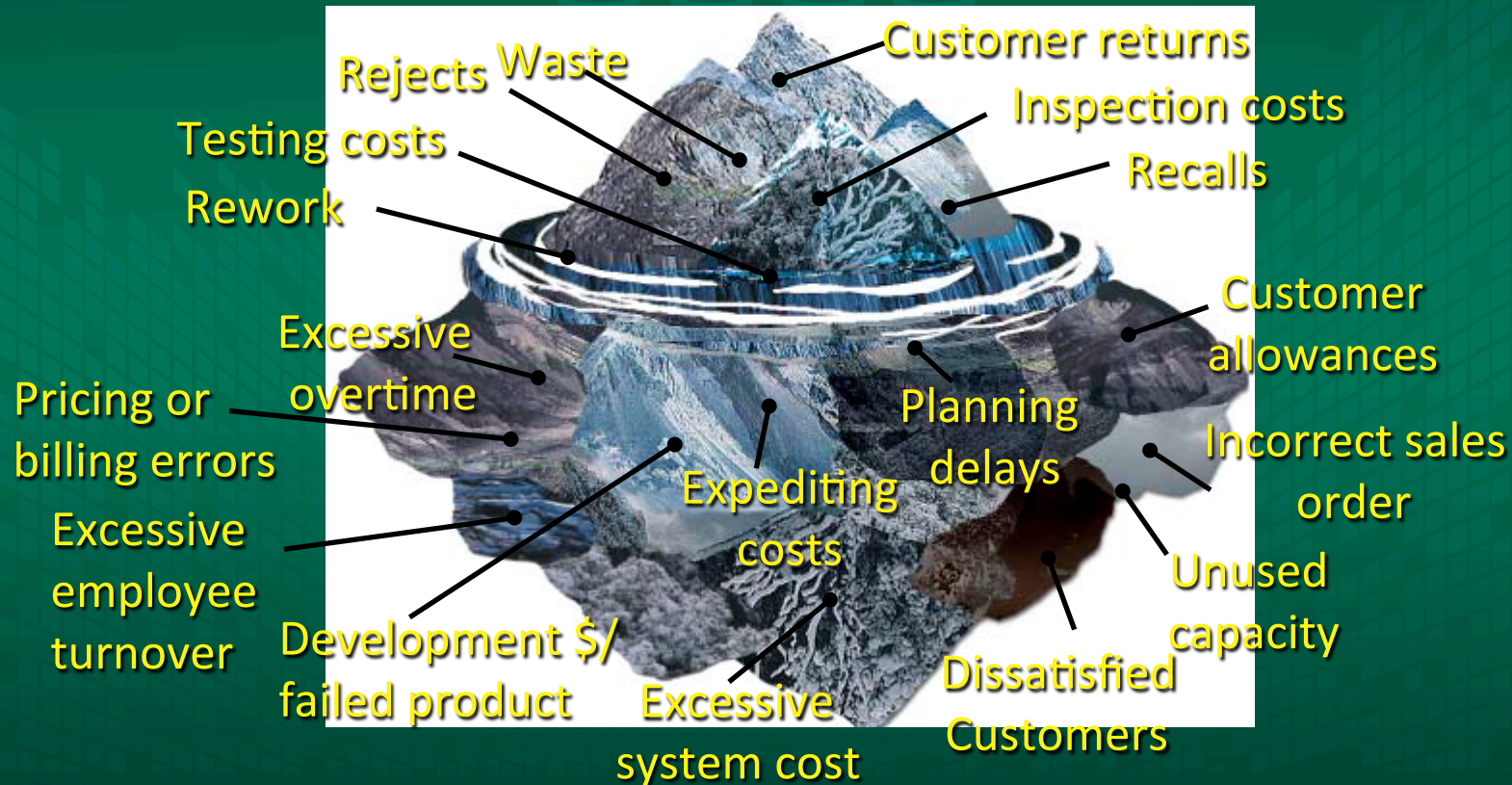


(4–5% of sales)



# Cost of Poor Quality (COPQ)

- When gaining a broader definition of poor quality the hidden portions of the iceberg becomes apparent



COPQ ranges from 15–25% of total cost.

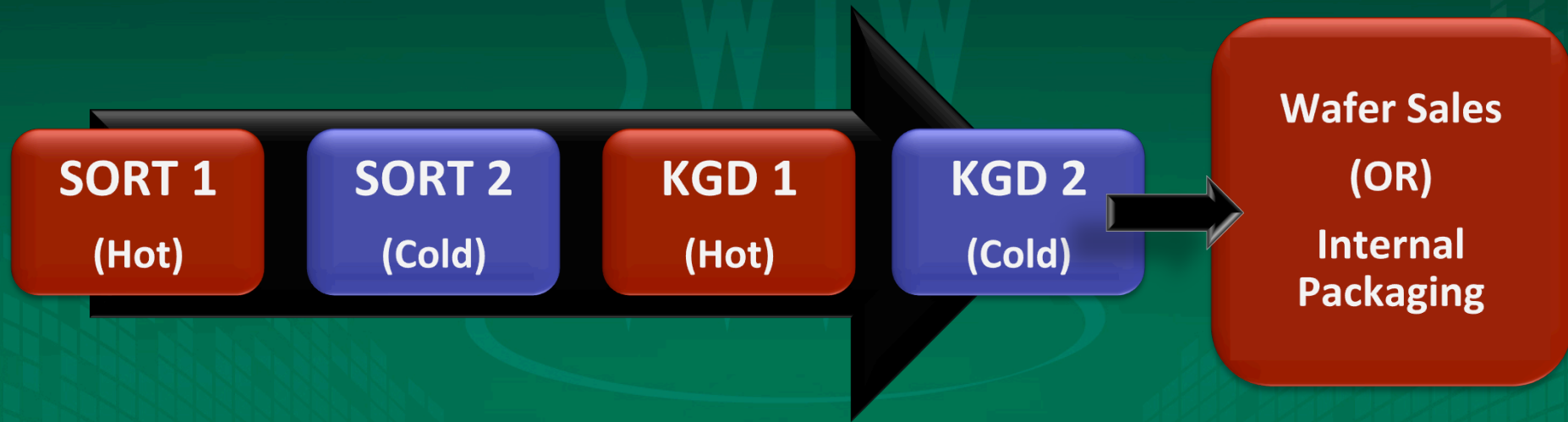




# KGD, High-Frequency, High-Parallel DRAM Wafer Test



# Typical Memory Test Flow



- **SORT**

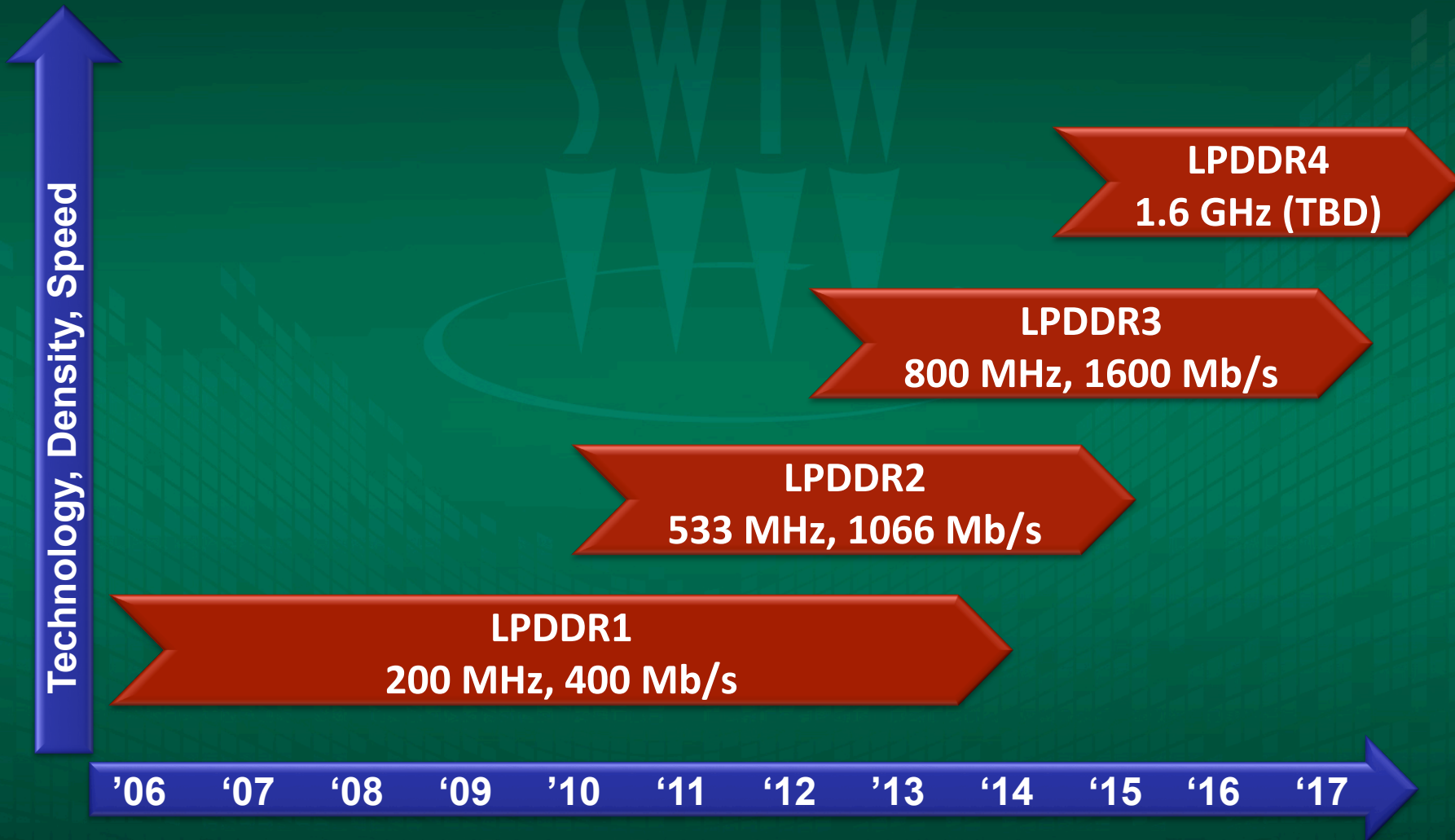
- Lower pin per DUT
- High parallelism
- Lower test frequency
- Full wafer contact
- Probe mark inspection

- **KGD**

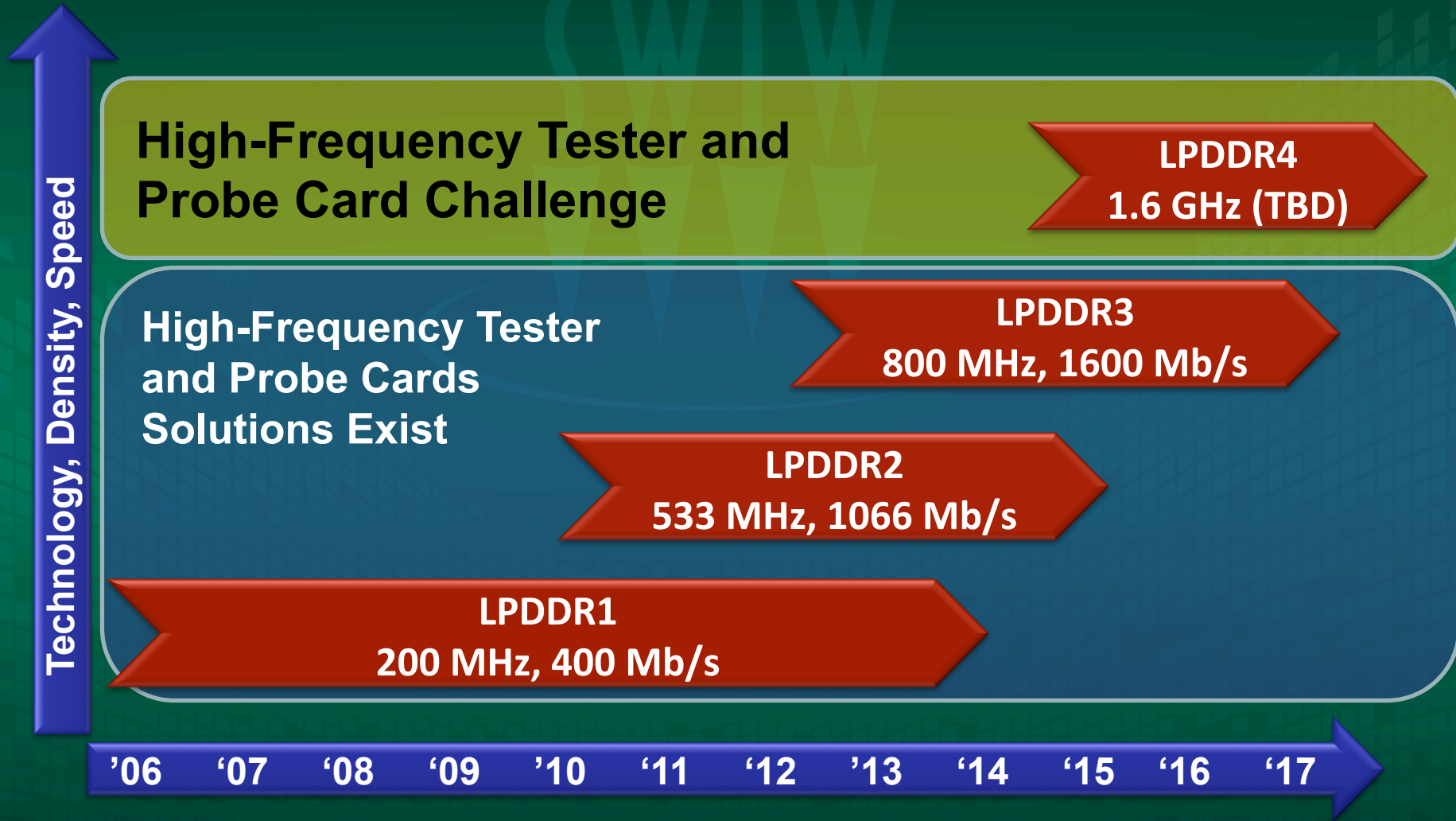
- Higher pin per DUT
- Low parallelism
- Higher test frequency
- Increased probe mark quantity



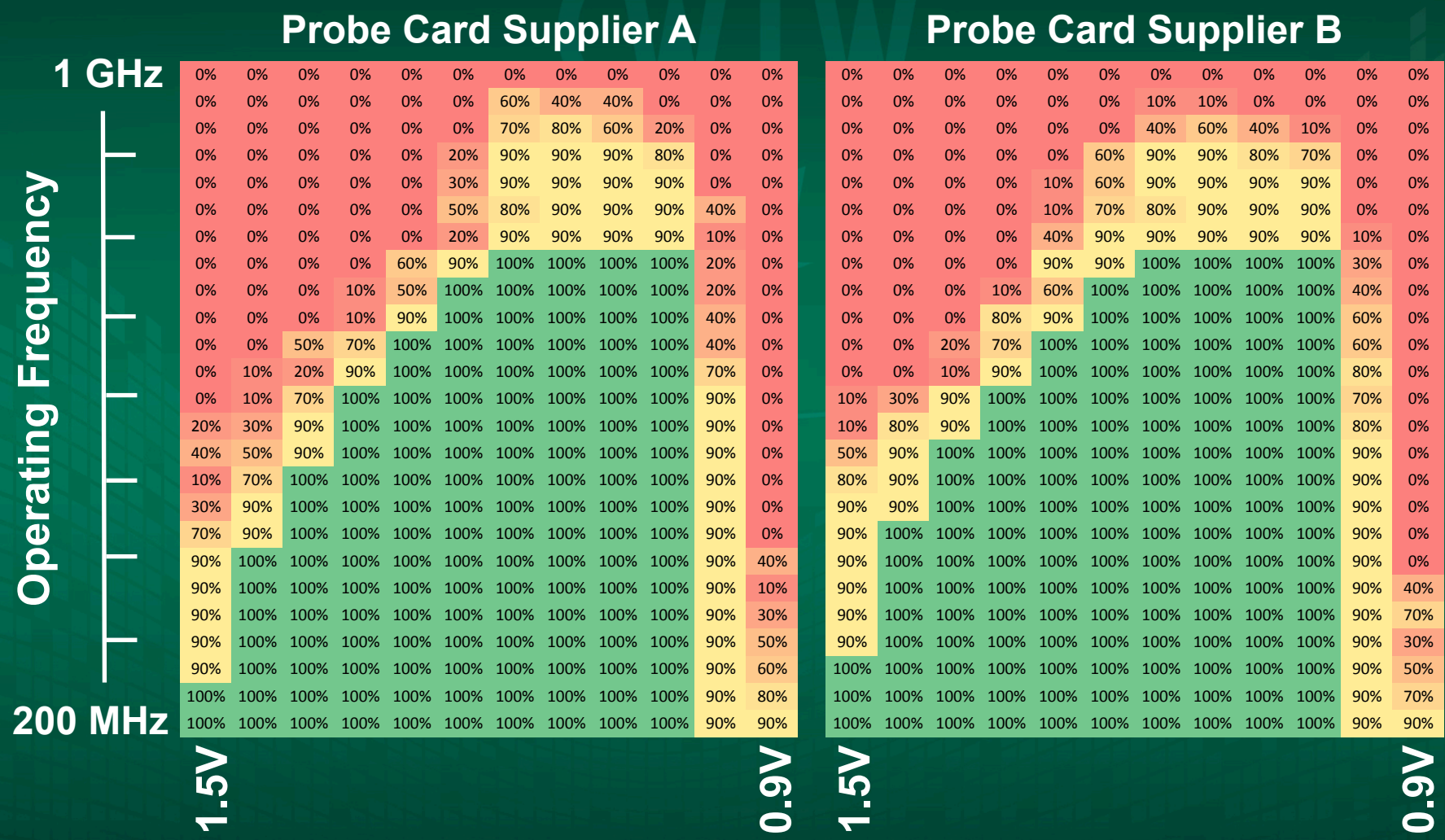
# Mobile LPDRAM Trend



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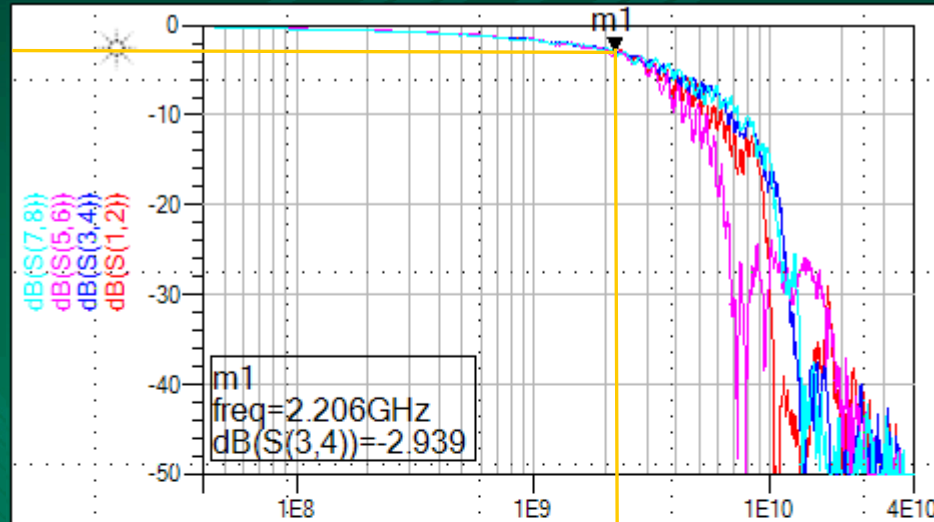


# Operating Frequency vs. Voltage Shmoo



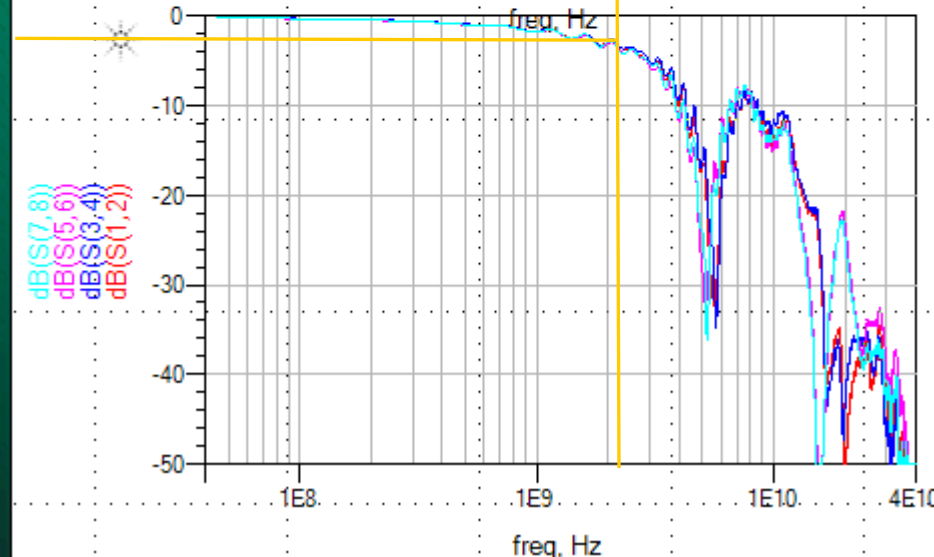
# Insertion Loss 800MHz Probe Card

-3dB Bandwidth



Probe Card  
Supplier A

-3dB Bandwidth

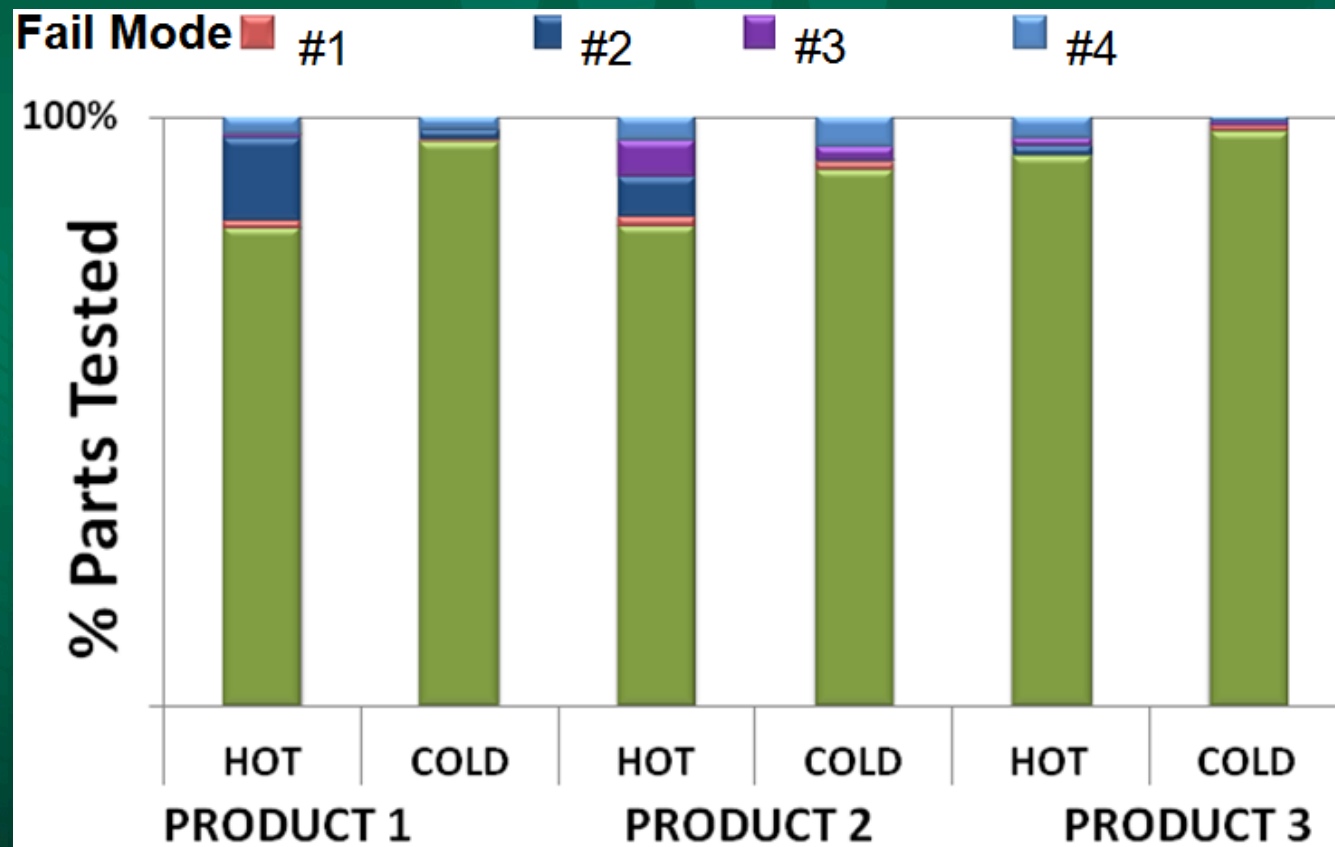


Probe Card  
Supplier B

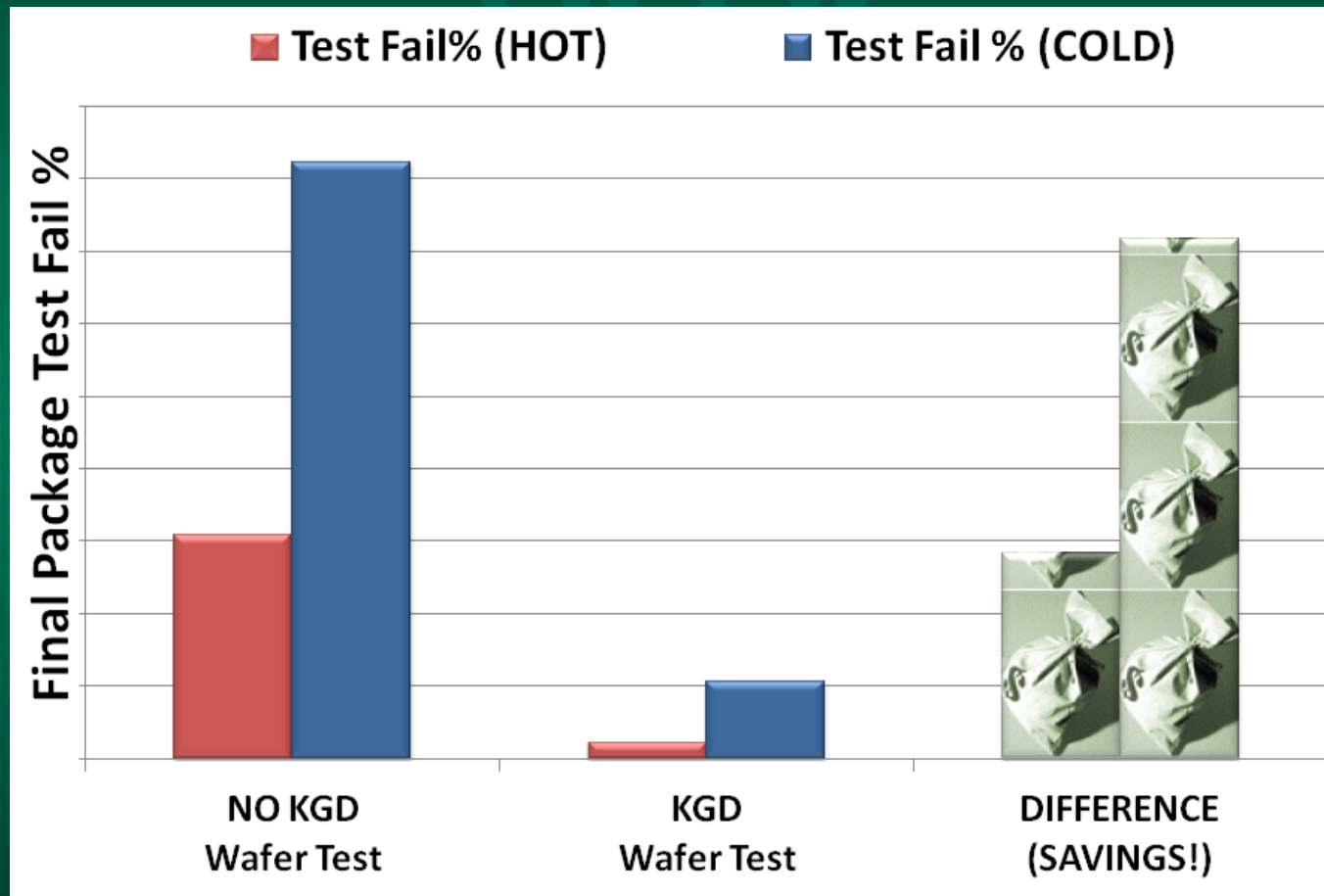


# KGD1 and KGD2 Wafer Test Fails

- Screening prior to packaging at max LPDDR2 frequency



# The Cost of Not Implementing KGD Wafer Test





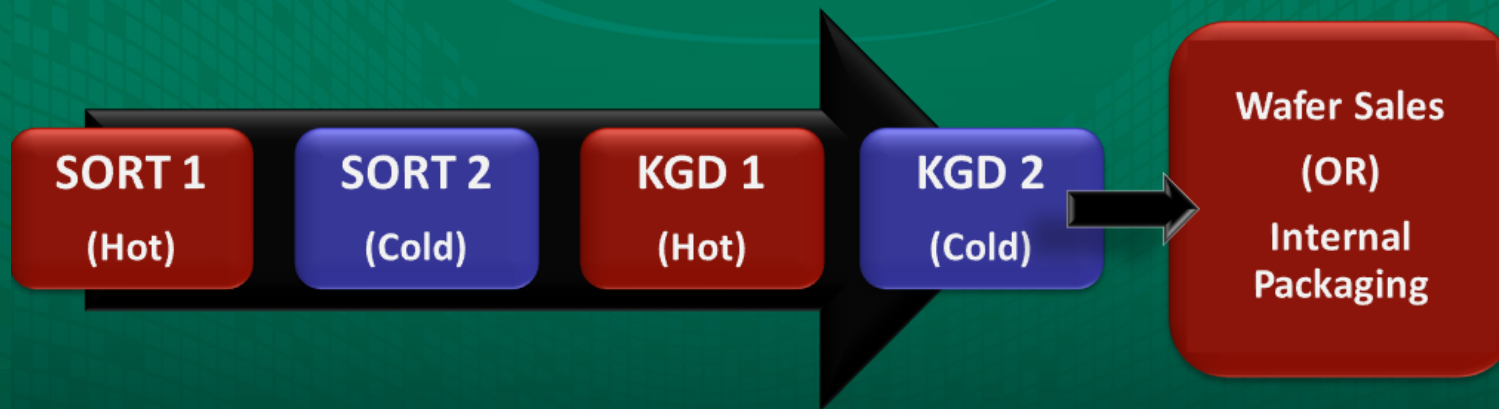
# KGD High-Frequency Solutions

- **Existing tester solutions:**
  - 1.2 GHz (2.4Gbs) to 1.6GHz (3.2Gbs)
- **Existing probe card solutions:**
  - 800 MHz (1.6 Gbs)
  - Signal line bandwidth of >2 GHz @ -3dB
  - Signal line trace length matching of <100ps



# What is Needed?

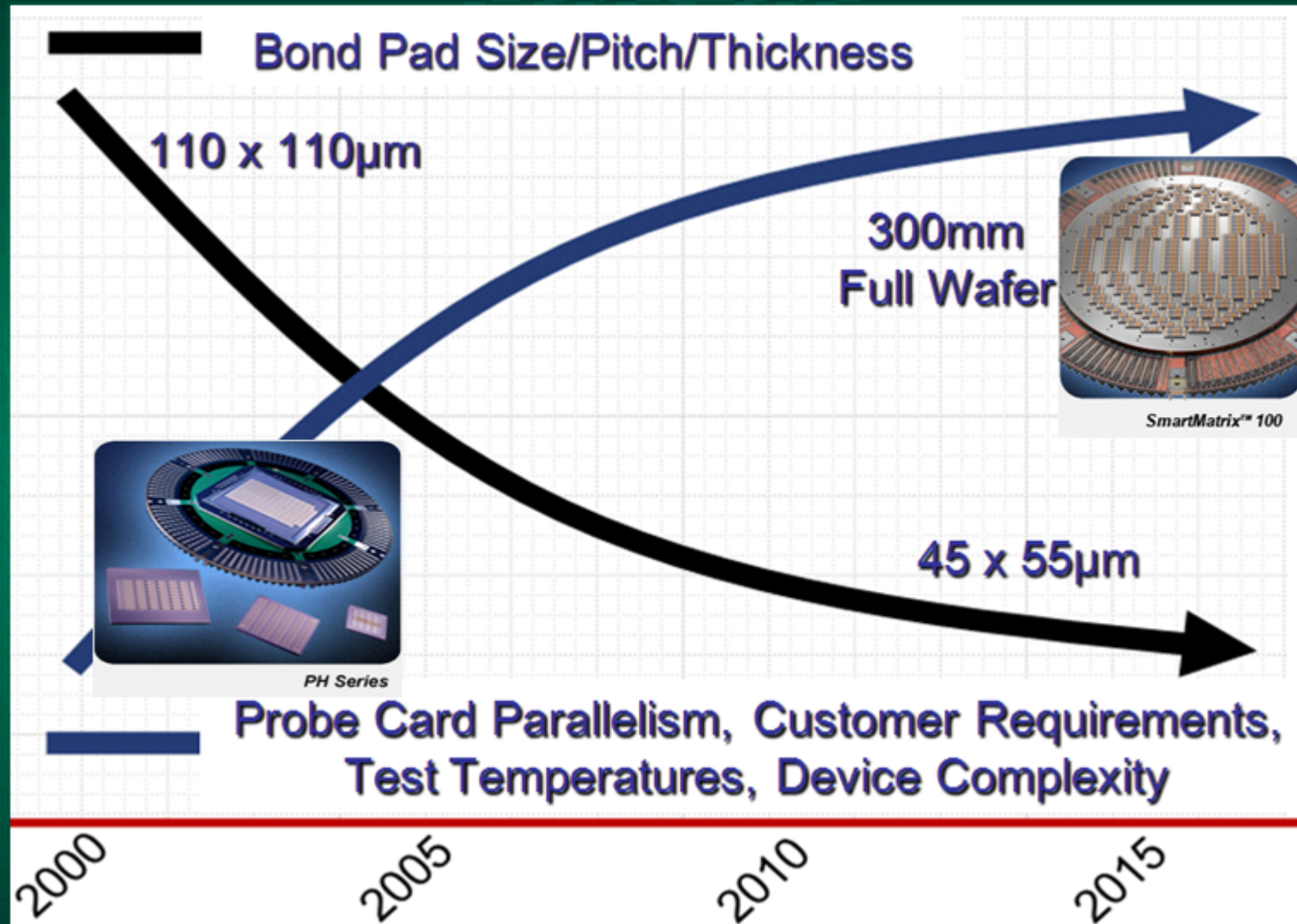
- High-frequency, high-parallelism solutions to enable LPDDR4 markets.



# Bond Pad Damage and Scrub Mark Placement

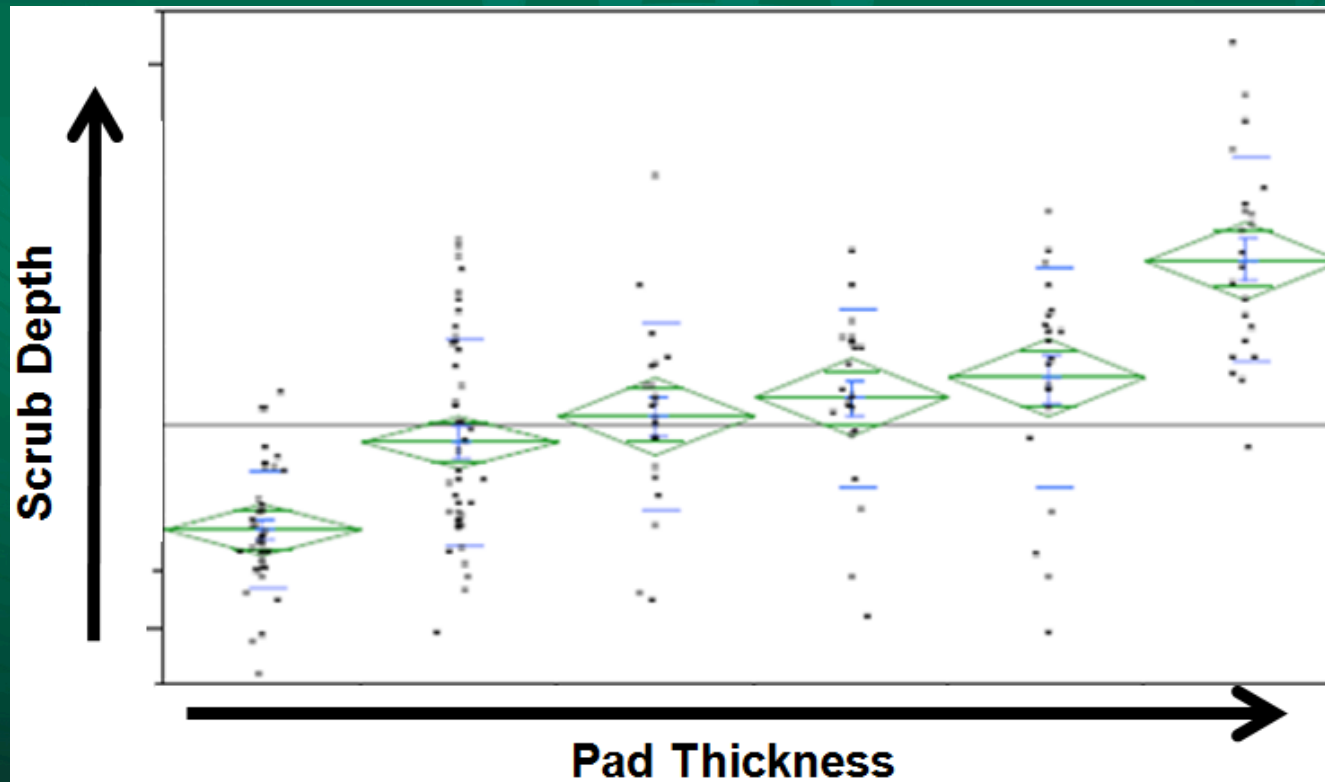


# Pad Size/Probe Card Complexity Trend



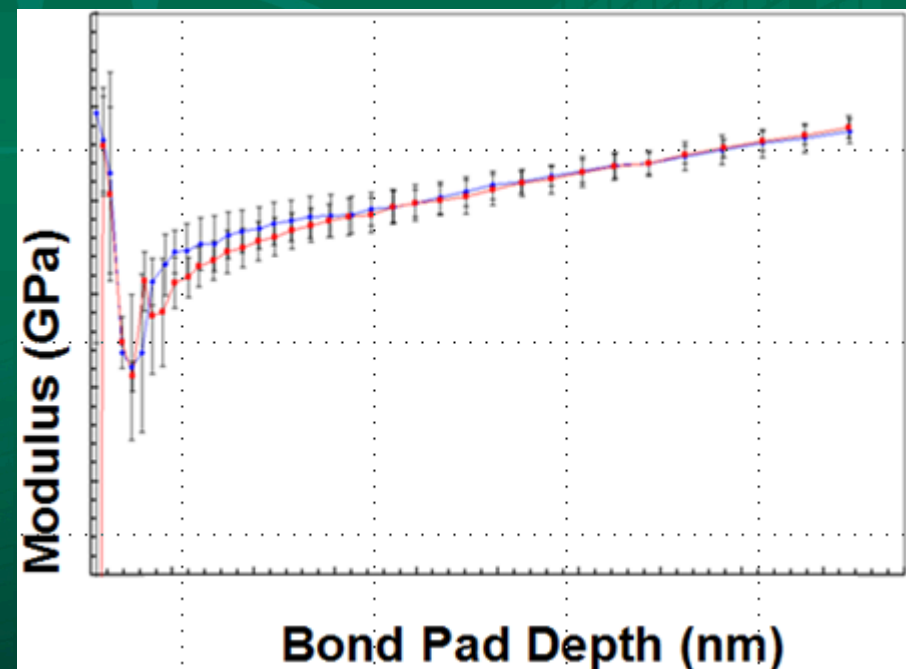
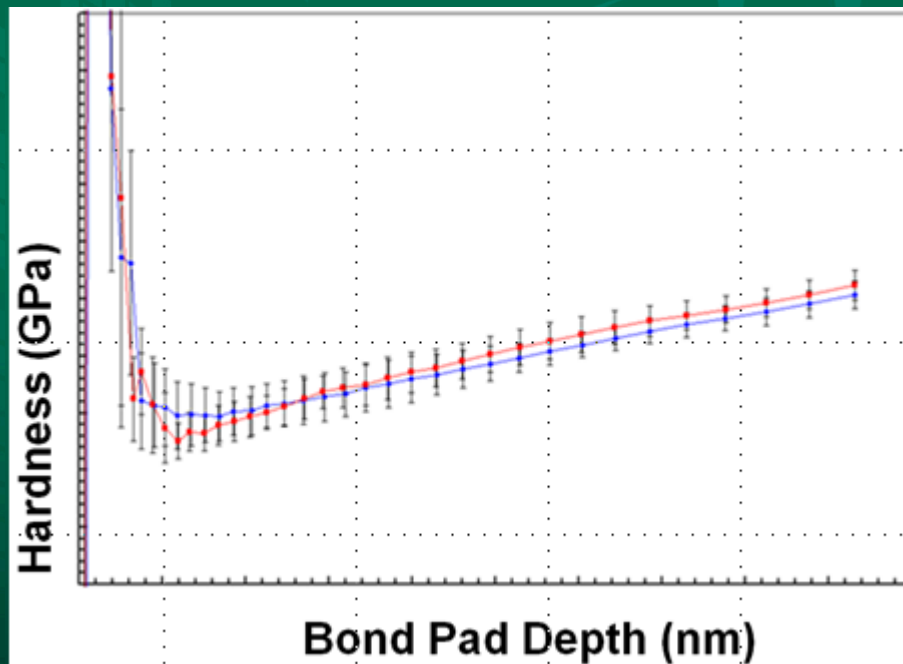
# Effect of Metal Thickness

- Scrub depth increases as bond pad material increases
  - Termed **Substrate Effect**: increased metal hardness & modulus in closer proximity to the underlying substrate



# Effect of Metal Thickness (cont.)

- Quantifying **Substrate Effect** : measured hardness and modulus of bond pad using nanoindentation
  - Hardness & modulus increase with measurement tool surface displacement



# Bond Pad Damage

- **Assembly and customer needs:**

- No punch through
- Disturbed area <25% of pad area
- Limit on maximum number of touchdowns

- **Internal design group wants:**

- Minimum pad size and pitch
- Reduced pad metal thickness
- Circuitry under pad (CuP)

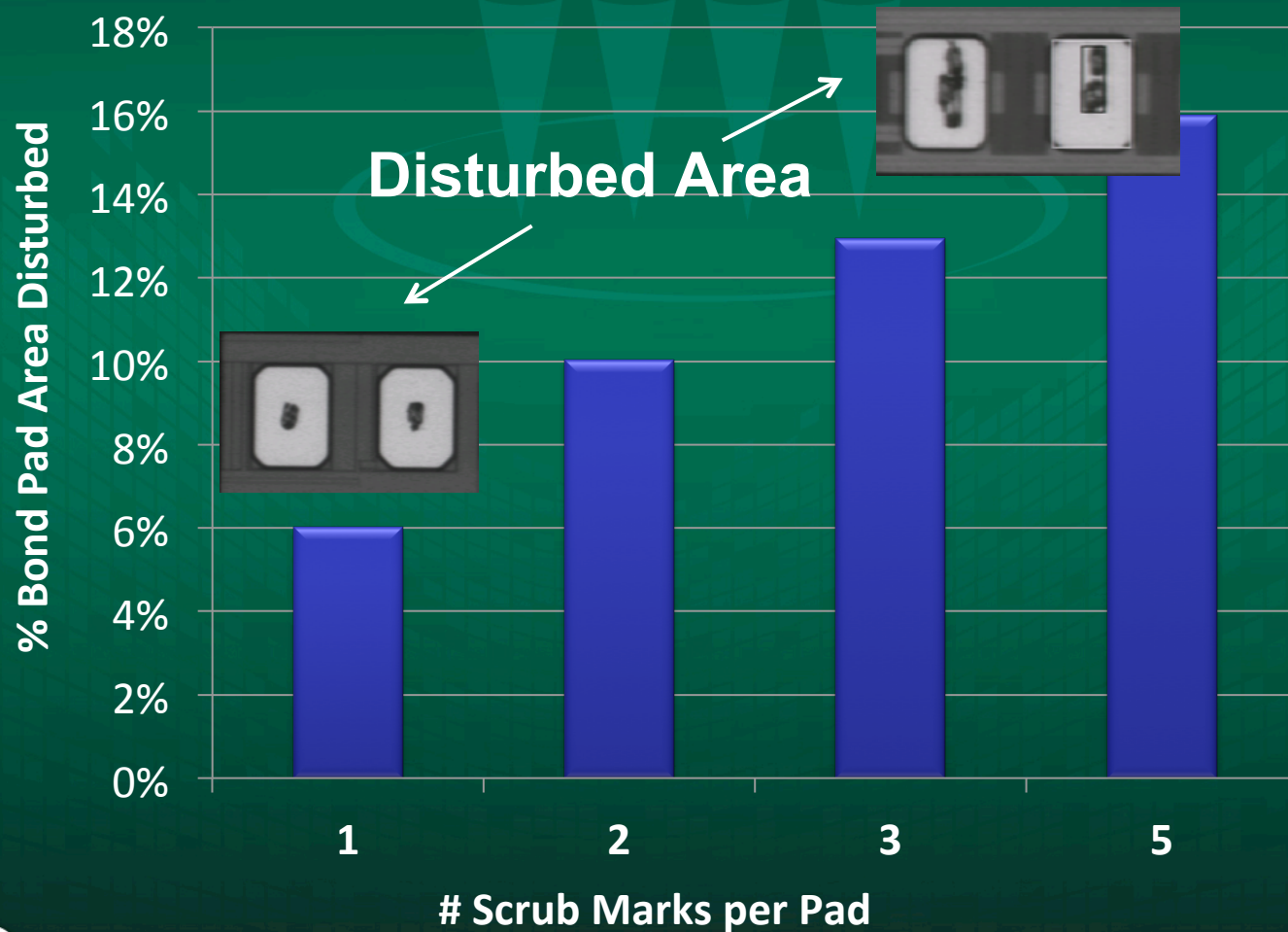


CONFLICTING  
REQUIREMENTS



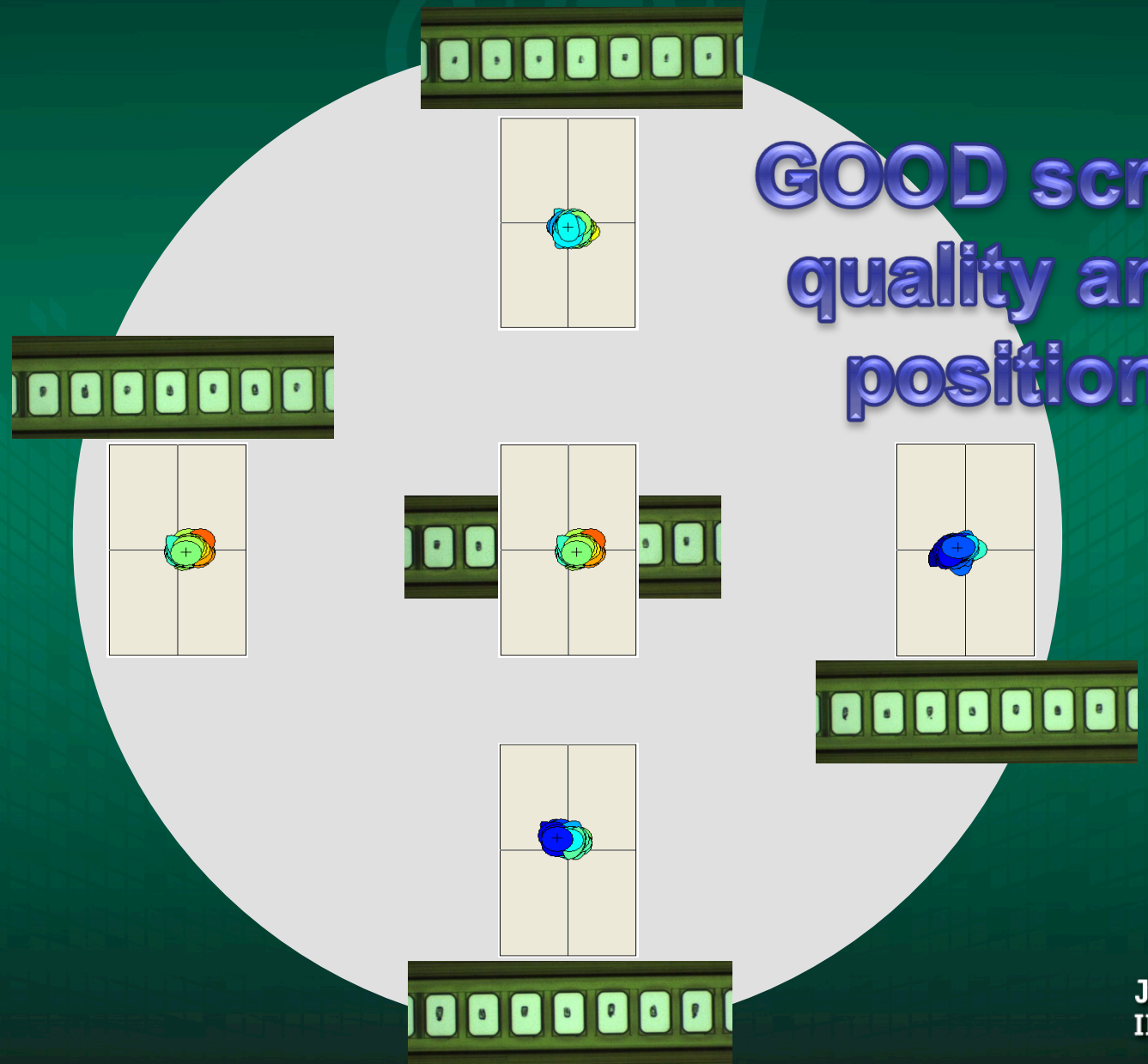
# Bond Pad Damage

- Pad area consumed by multiple wafer test steps





# Full-Wafer Scrub Mark Placement



**GOOD scrub  
quality and  
position**



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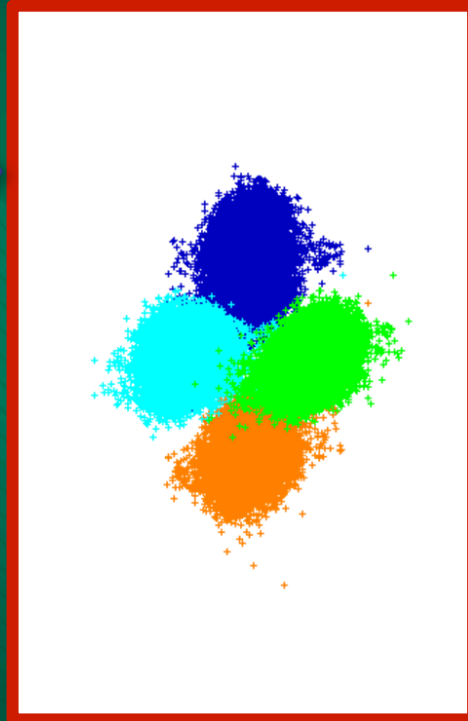
# Full-Wafer Scrub Mark Placement



**BAD scrub  
quality and  
position**

# Bond Pad Damage – TBLR Analysis

GOOD!



— Bond Pad Edge

● Extent of Scrub Mark Top

● Extent of Scrub Mark Bottom

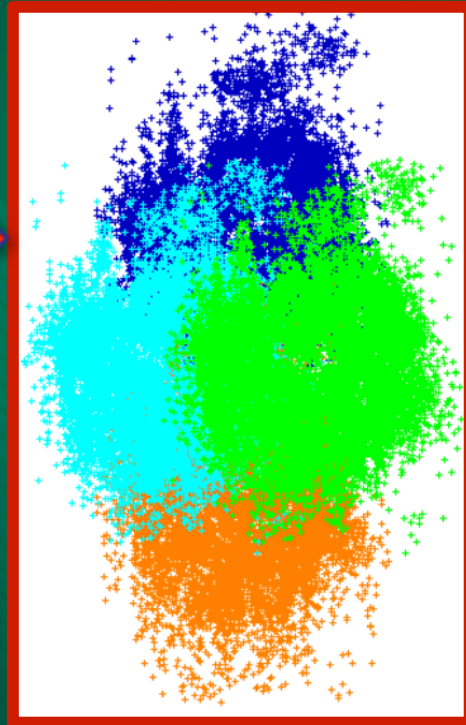
● Extent of Scrub Mark Left

● Extent of Scrub Mark Right

- >20K scrub mark data overlay
- Good centering and tight distribution

# Bond Pad Damage – TBLR Analysis

**BAD!**



— Bond Pad Edge

● Extent of Scrub Mark Top

● Extent of Scrub Mark Bottom

● Extent of Scrub Mark Left

● Extent of Scrub Mark Right

- >20K scrub mark data overlay
- Good centering and tight distribution

# What is Needed?

- **Reduced pad damage**
  - Low force probes
  - Reduced scrub length
- **Greater probe card z-compliance (Max OD)**
- **Efficient inline probe mark inspection methods**

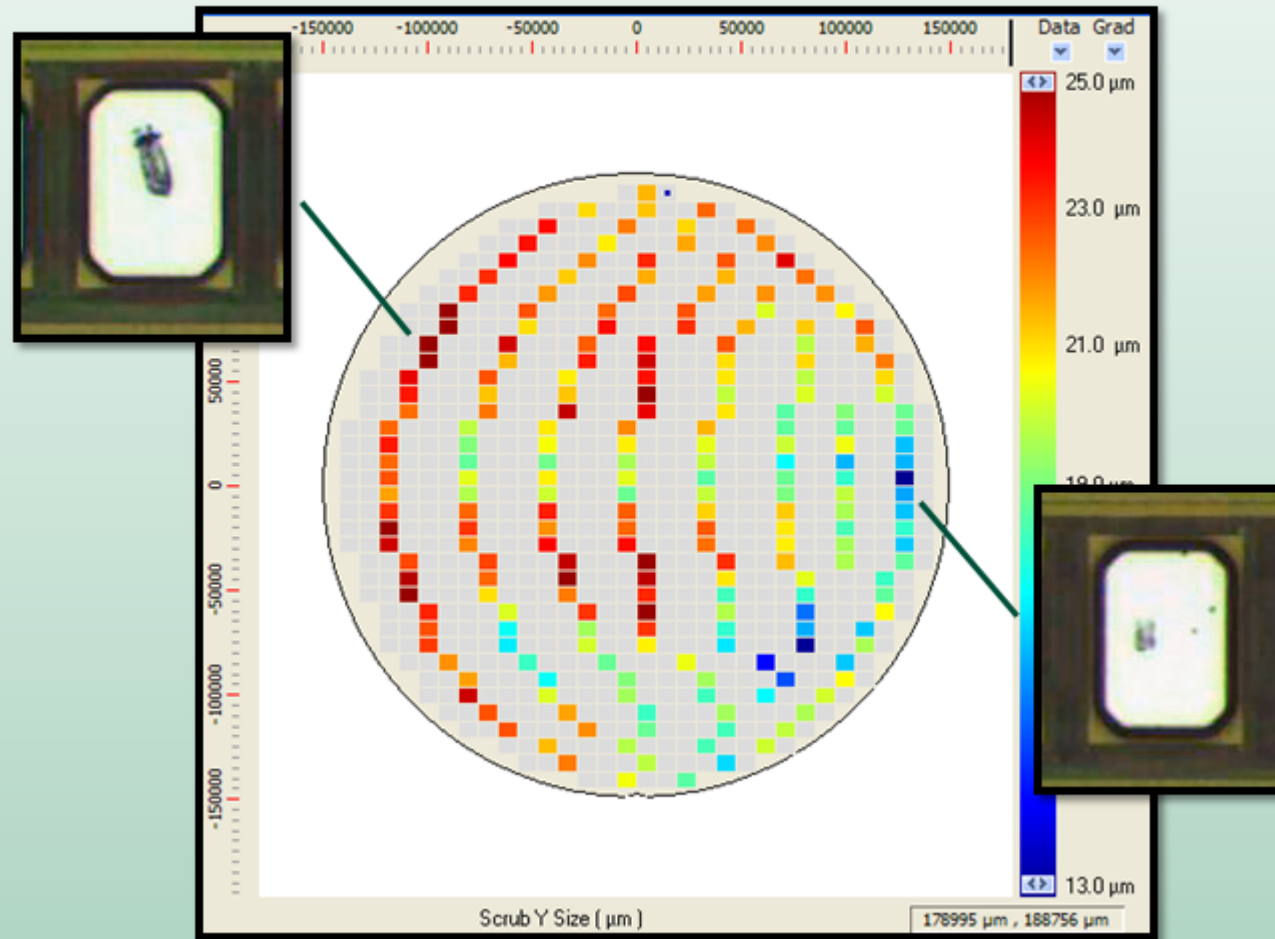


# Test Cell Mechanical Tolerance Stackup



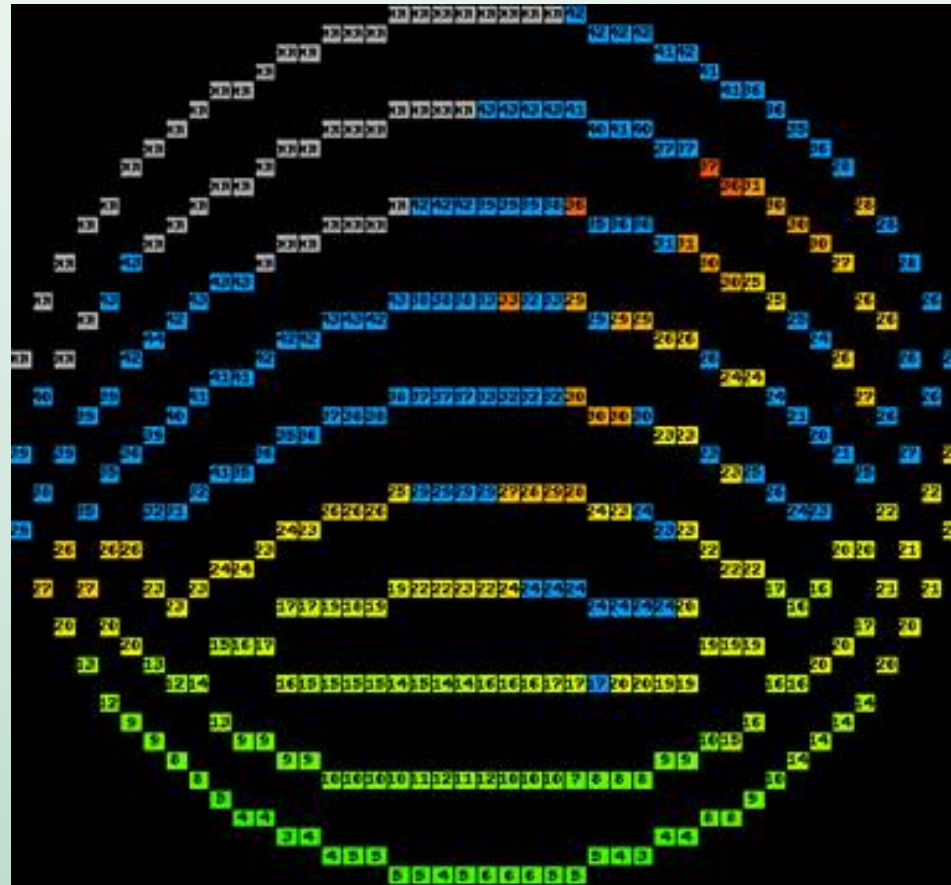
# Cost of Increased Planarity Variation

## Physical Damage – Scrub Length Contour Plot



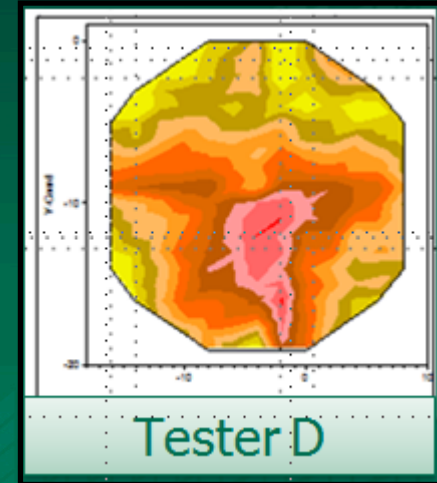
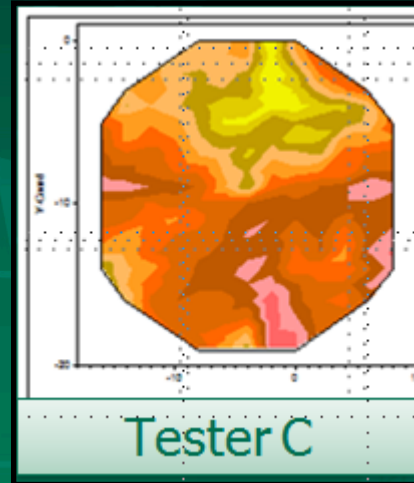
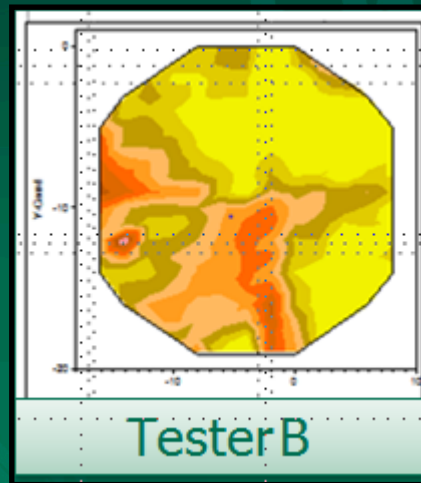
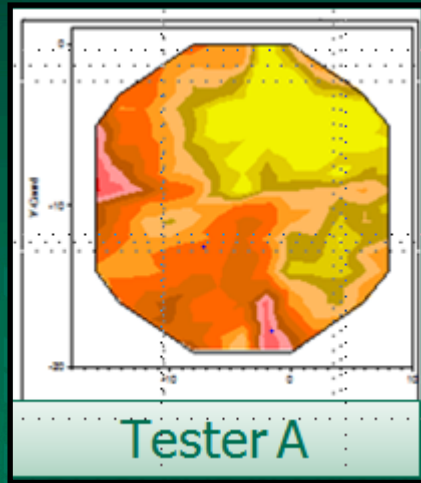
# Cost of Increased Planarity Variation

## Electrical Performance – Continuity Contour Plot

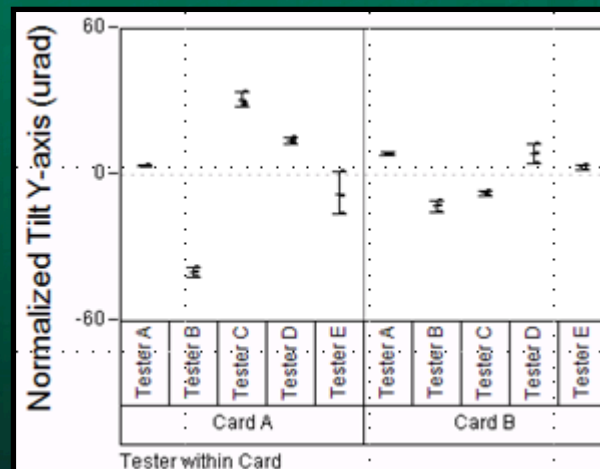
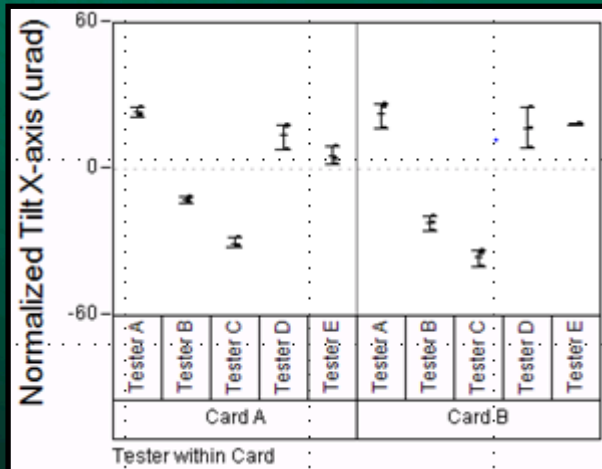




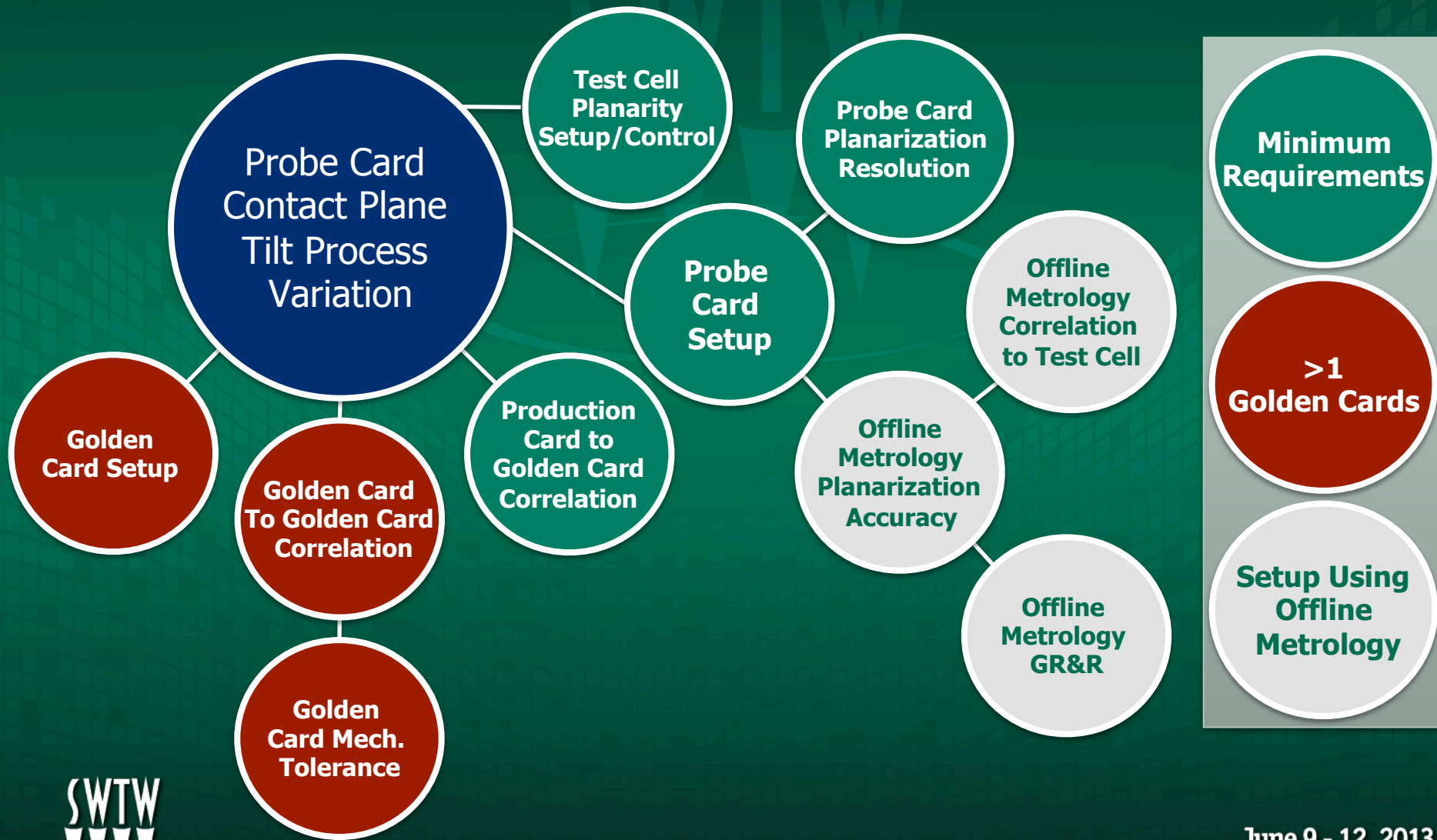
# Cost of Manufacturing Support



## Tester-to-Tester Planarity Variation



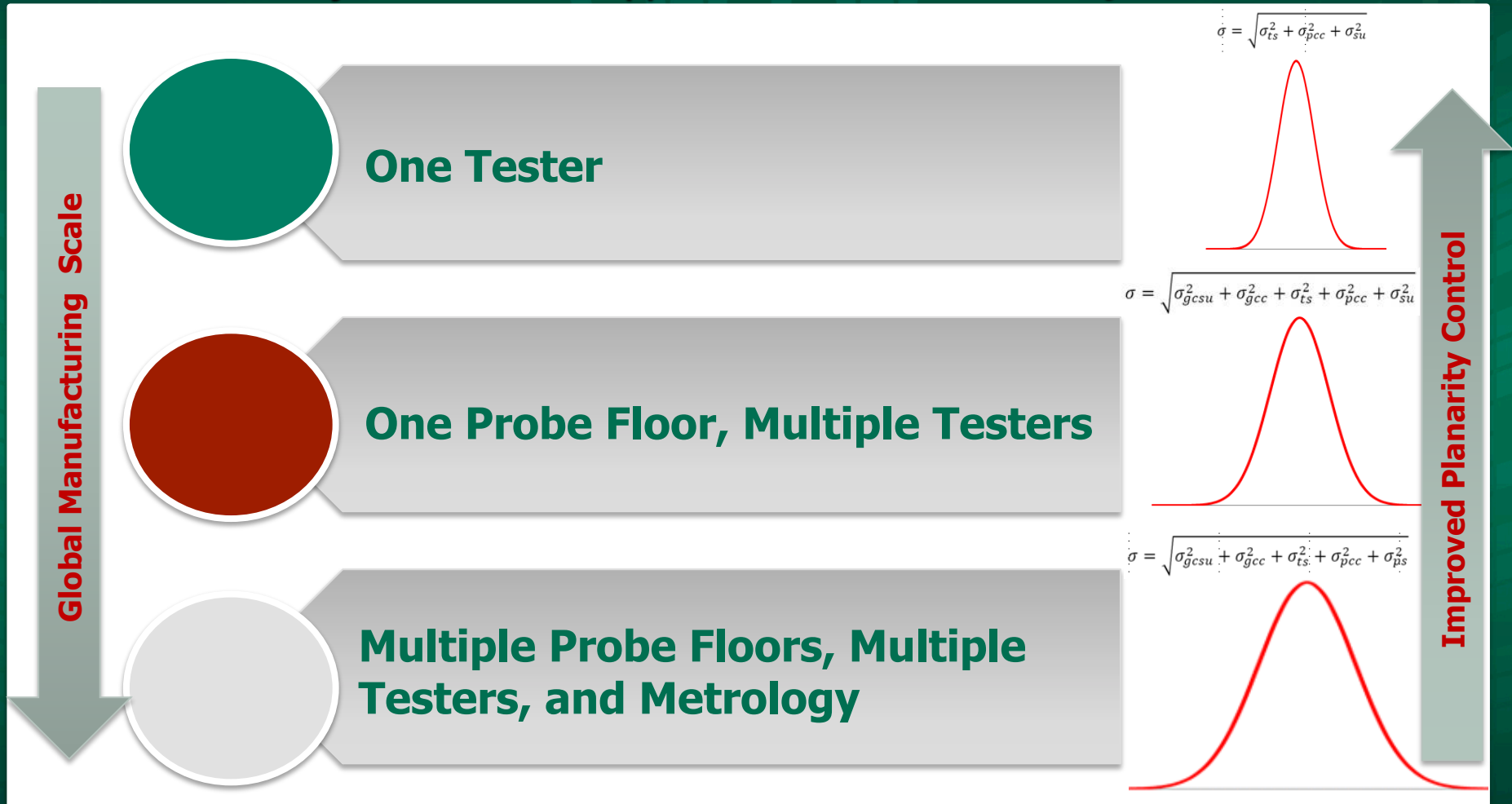
# Test Cell Planarity Process Control



# Test Cell Planarity Support Model

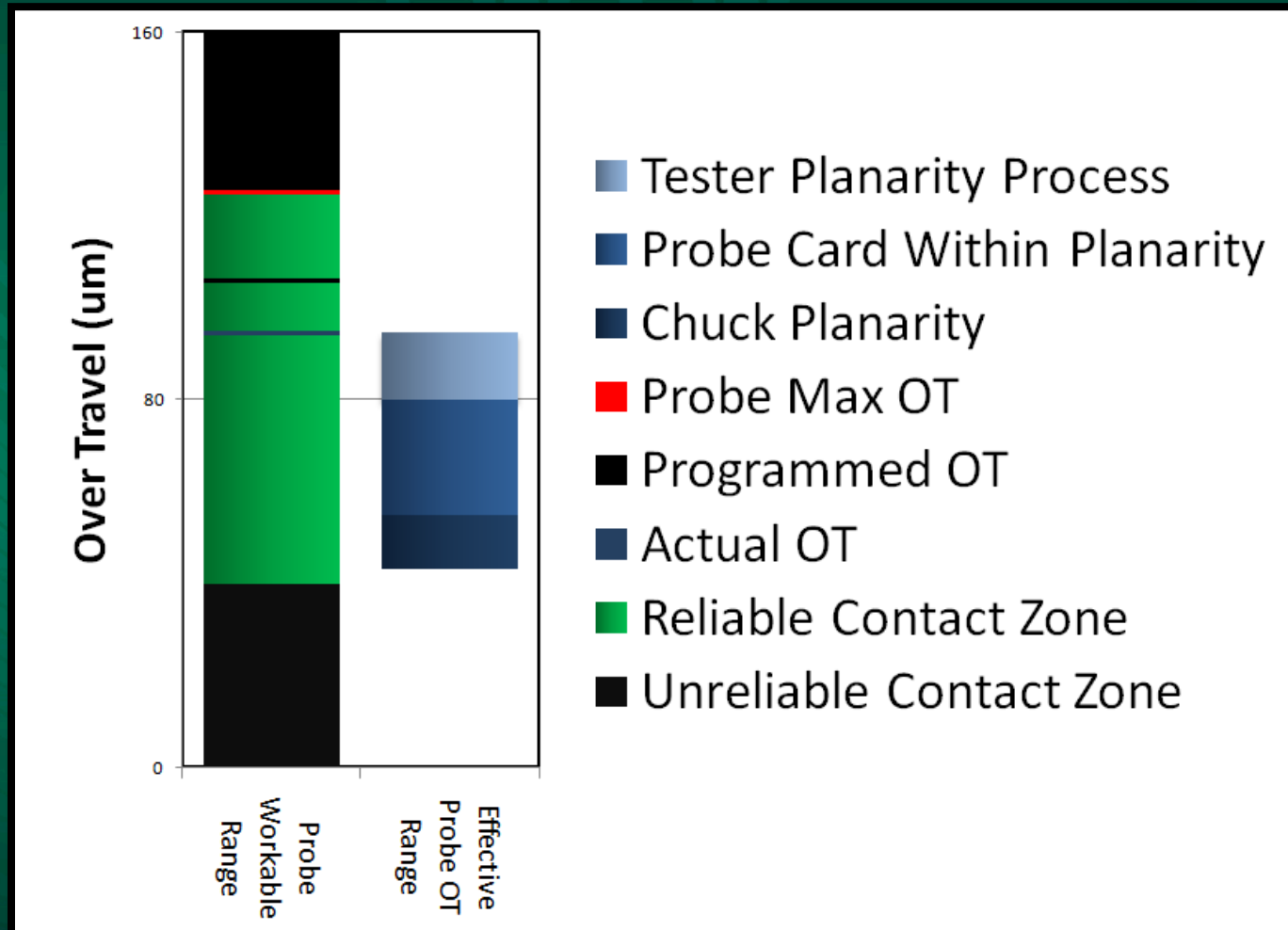
Planarity Maintenance/Support Model

Planarity Variation Probe Floor



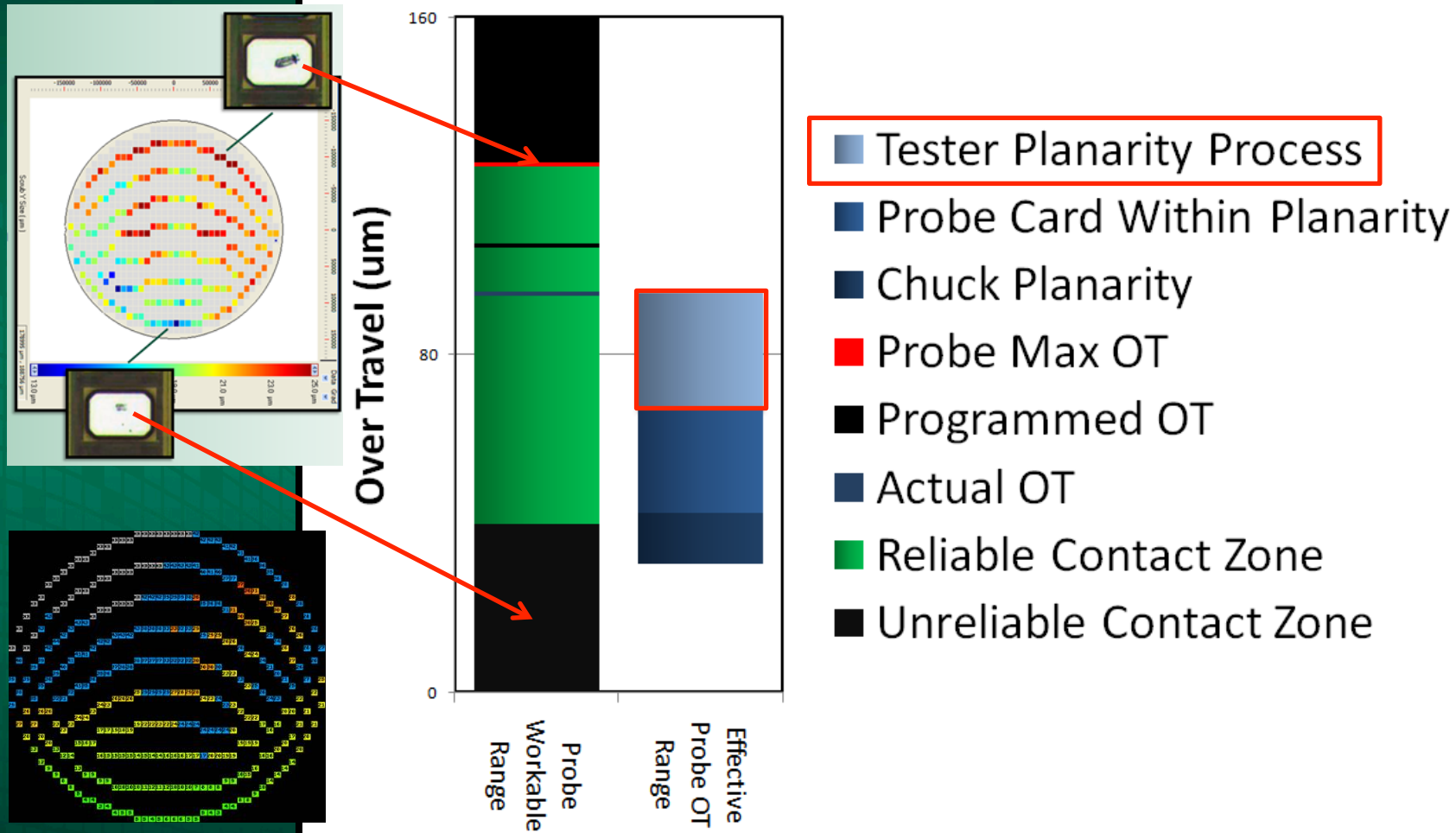
# Probe Range vs. Test Cell Planarity

## 1 Golden Card, Probe Planarized on Tester Cell



# Probe Range vs. Test Cell Planarity

## Offline Metrology Probe Card Setup + >1 Golden Cards



# What is Needed?

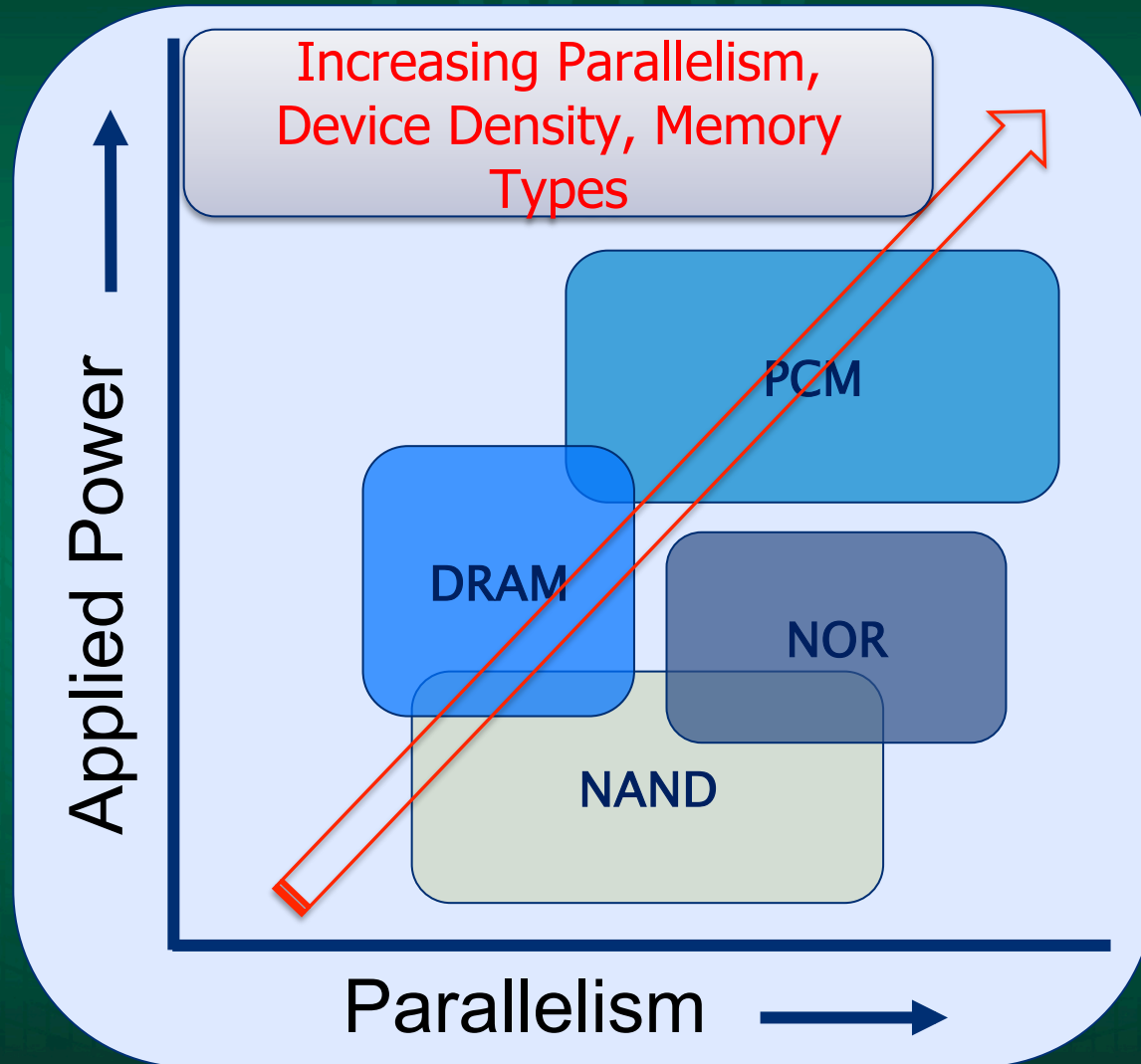
- **Equipment Designed for Manufacturing (DFM)**
  - Innovative, integrated test cell solutions
  - Tighter probe card planarity
  - Greater probe card z-compliance



# Thermal Management

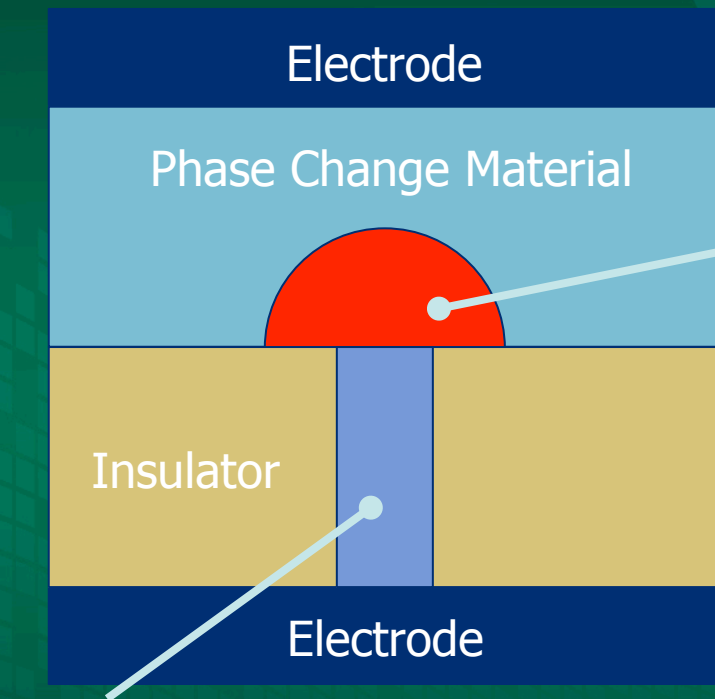


# 2013 Memory Landscape

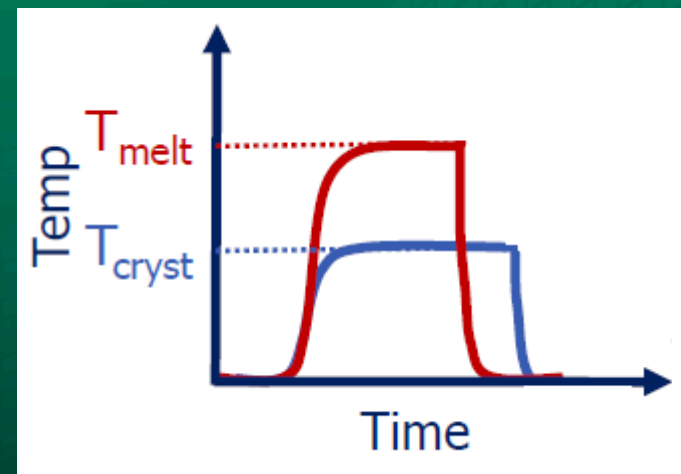
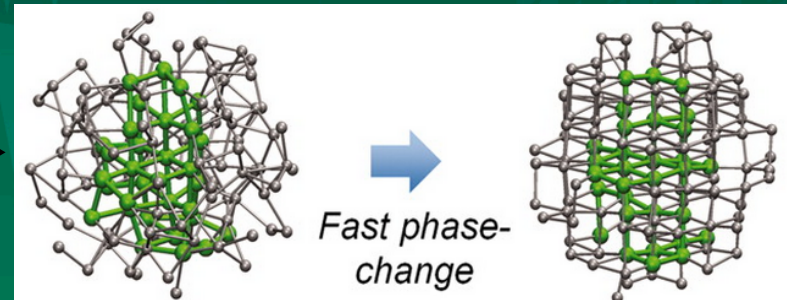




# Phase Change Memory (PCM)



Cell  
Region



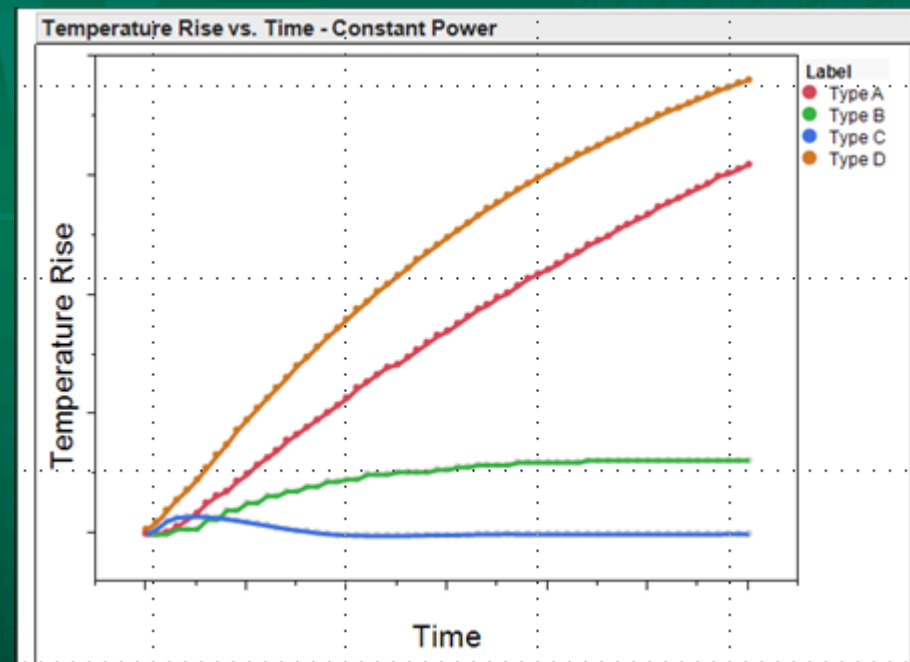
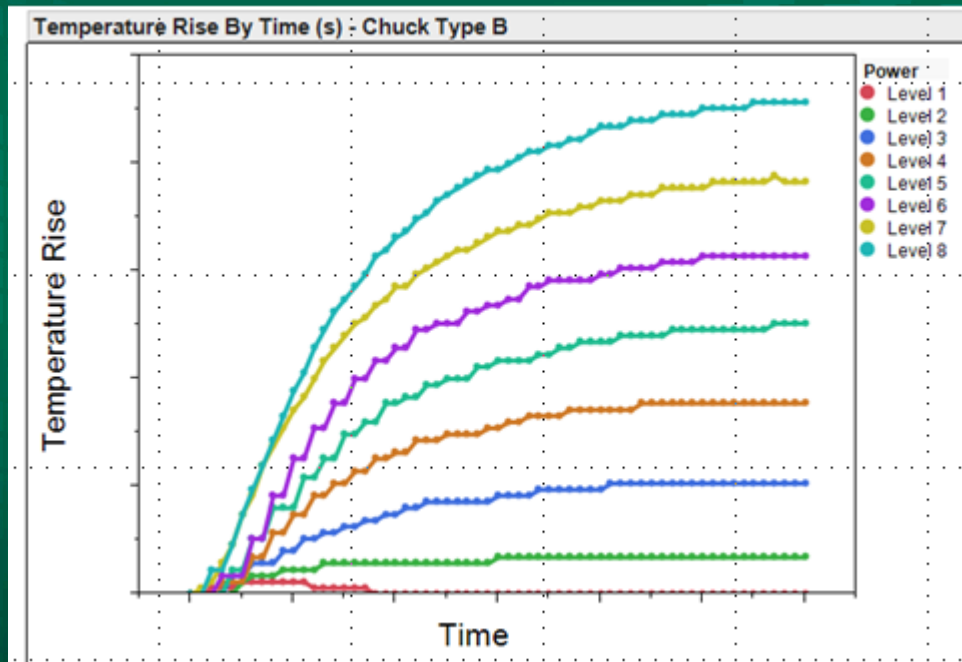
# Device Characterization

- Characterize **power curves** and **device temperature** during functional test flow



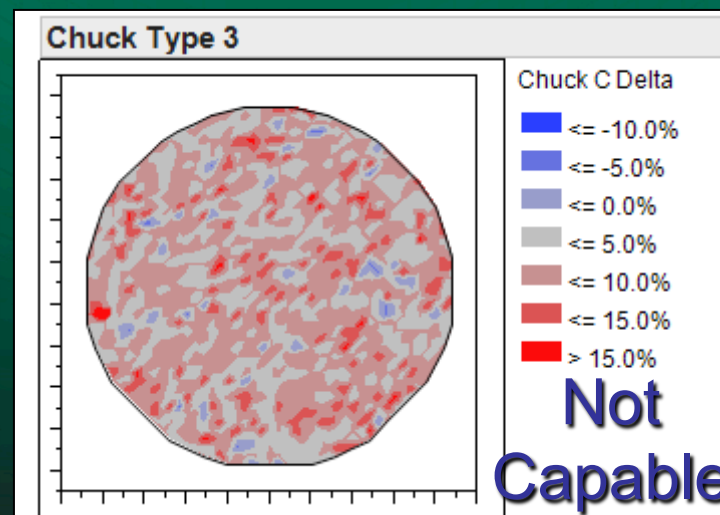
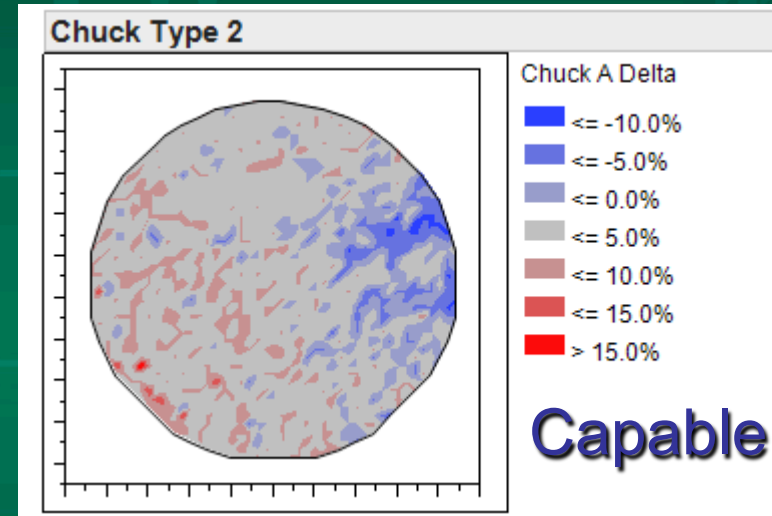
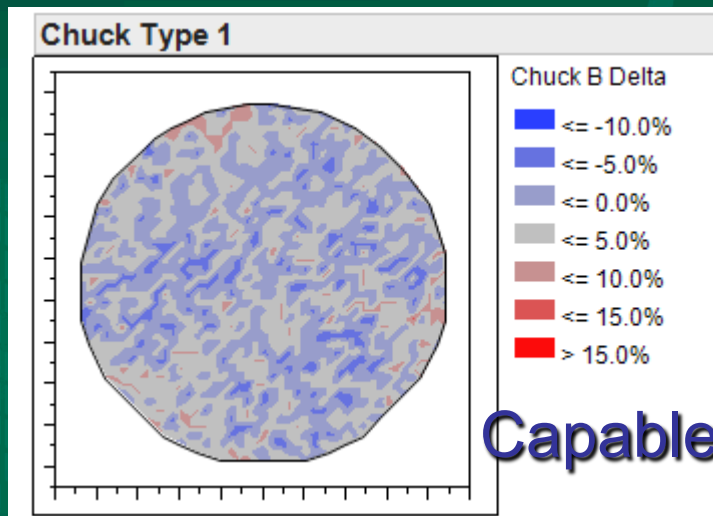
# Equipment Characterization

- Characterize **chuck response to applied power** and benchmark performance



# Analyze Test Data

- Die temperature vs. chuck temperature



# What is Needed?

- Innovative power/thermal management solutions for high-parallel applications.
- Diligent characterization of device power dissipation requirements to allow informed equipment selection.

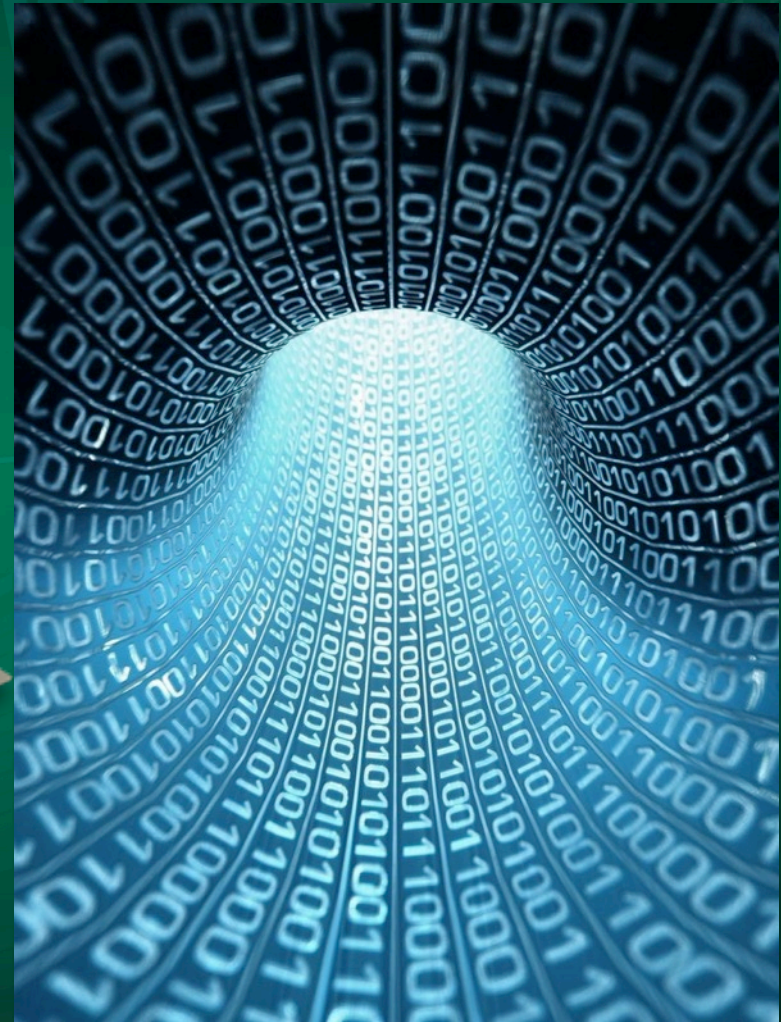
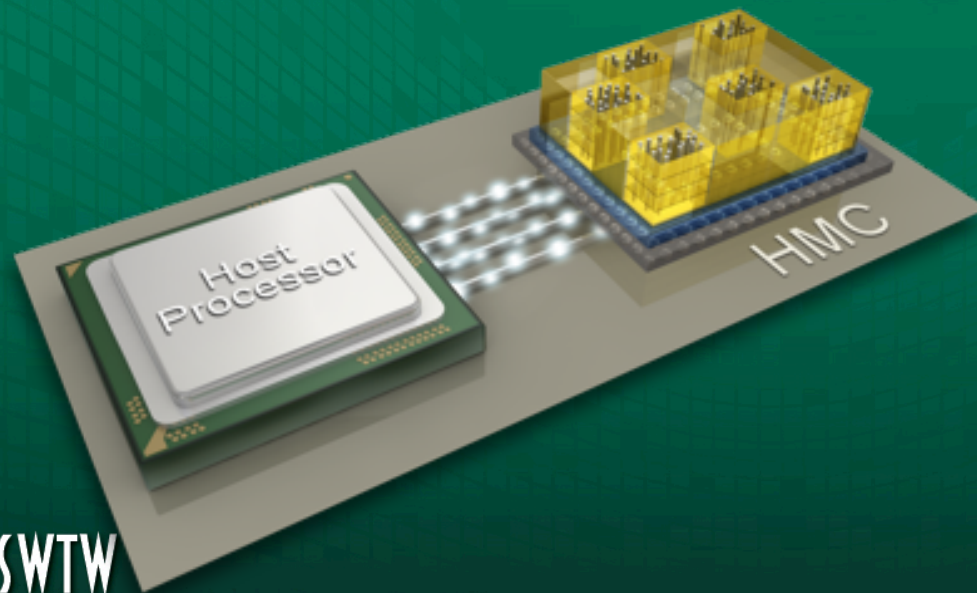


# Future Memory Product Challenges



# Future Challenges - Memory Revolution

- Global demand for mobility, exponential data growth, cloud service requirements, storage server capabilities



# Conclusion

- **LPDDR4 challenges** current probe roadmap. Opportunity exists to enable new capability.
- **Integrated test cell solutions (DFM)** Designed for Manufacture, (metrology, prober, probe card)
- **Emerging memory** devices are driving demanding thermal management solutions.
- **Cost of Quality** has to be addressed through industry collaboration (standards around test for manufacturing).





**Thank You!**

